

(19)



(11)

EP 2 085 813 B1

(12)

EUROPEAN PATENT SPECIFICATION

(45) Date of publication and mention
of the grant of the patent:
01.01.2014 Bulletin 2014/01

(51) Int Cl.:
G02F 1/1335 ^(2006.01) **G02F 1/1343** ^(2006.01)

(21) Application number: **07806943.2**

(86) International application number:
PCT/JP2007/067511

(22) Date of filing: **07.09.2007**

(87) International publication number:
WO 2008/047517 (24.04.2008 Gazette 2008/17)

(54) **LIQUID CRYSTAL DISPLAY AND METHOD FOR MANUFACTURING LIQUID CRYSTAL DISPLAY**

FLÜSSIGKRISTALLANZEIGE UND VERFAHREN ZUM HERSTELLEN EINER
FLÜSSIGKRISTALLANZEIGE

DISPOSITIF D’AFFICHAGE À CRISTAUX LIQUIDES ET PROCÉDÉ DE FABRICATION DE CELUI-CI

(84) Designated Contracting States:
**AT BE BG CH CY CZ DE DK EE ES FI FR GB GR
HU IE IS IT LI LT LU LV MC MT NL PL PT RO SE
SI SK TR**

(30) Priority: **18.10.2006 JP 2006284206**

(43) Date of publication of application:
05.08.2009 Bulletin 2009/32

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Description

TECHNICAL FIELD

[0001] The present invention relates to a reflection-type or transfective-type liquid crystal display device capable of performing display by utilizing reflected light.

BACKGROUND ART

[0002] Liquid crystal display devices include the transmission-type liquid crystal display device which utilizes backlight from behind the display panel as a light source for displaying, the reflection-type liquid crystal display device which utilizes reflected light of external light, and the transfective-type liquid crystal display device which utilizes both external light and backlight as light sources. The reflection-type liquid crystal display device and the transfective-type liquid crystal display device are **characterized in that** they have smaller power consumptions than that of the transmission-type liquid crystal display device, and their displayed images are easy to see in a bright place. The transfective-type liquid crystal display device is **characterized in that** the display is easier to see than that of the reflection-type liquid crystal display device, even in a dark place.

[0003] FIG. 15 is a cross-sectional view of an active matrix substrate 100 in a conventional reflection-type liquid crystal display device (e.g., Patent Document 1).

[0004] As shown in FIG. 15, the active matrix substrate 100 includes an insulative substrate 101, as well as a gate layer 102, a gate insulating layer 104, a semiconductor layer 106, a metal layer 108, and a reflective layer 110, which are stacked on the insulative substrate 101. After being stacked on the insulative substrate 101, the gate layer 102, the gate insulating layer 104, the semiconductor layer 106, and a metal layer 108 are subjected to etching by using one mask, thus being formed so as to have an island-like multilayer structure. Thereafter, the reflective layer 110 is formed on this multilayer structure, whereby a reflective layer 112 having recesses/protrusions is formed. Although not shown, transparent electrodes, a liquid crystal layer, a color filter substrate (CF substrate), and the like are formed above the active matrix substrate 100.

[Patent Document 1] Japanese Laid-Open Patent Publication No. 9-54318

[0005] US 2002/0018161 A1 refers to a TFT substrate, where a TFT and a plurality of projecting portions are formed on a substrate. The projecting portions are formed simultaneously with the TFT by patterning methods. Each of the projecting portions consists of the layer of a gate electrode and a gate insulating film layer. A plurality of pixel electrodes having a light reflecting property are provided over the projecting portions. The pixel electrodes have also flat portions. The projecting portions

may be separated from each other or may at least partially be connected to each other.

DISCLOSURE OF INVENTION

PROBLEMS TO BE SOLVED BY THE INVENTION

[0006] In the aforementioned active matrix substrate 100, portions of the reflective layer 110 are formed so as to reach the insulative substrate 101 in portions where a gate layer 102 and the like are not formed (i.e., portions between the islands, hereinafter referred to as "gap portions"). Therefore, in the gap portions, the surface of a reflection surface 112 is recessed in the direction of the insulative substrate 101, thus forming deep dents (or recesses).

[0007] In the reflection-type or transfective-type liquid crystal display device, in order to perform bright display by utilizing reflected light, it is necessary to allow incident light entering from various directions to be reflected by the reflection surface more uniformly and efficiently over the entire display surface. For this purpose, it is better if the reflection surface is not completely planar but has moderate recesses/protrusions.

[0008] However, since the reflection surface 112 of the aforementioned active matrix substrate 100 has deep dents, light is unlikely to reach the reflection surface located on the bottoms of the dents, and even if at all light reaches there, the reflected light thereof is unlikely to be reflected toward the liquid crystal panel. Therefore, the aforementioned conventional liquid crystal display device has a problem in that the reflected light is not effectively used for displaying. Furthermore, there is also a problem in that, since many portions of the reflection surface 110 have a large angle relative to the display surface of the liquid crystal display device, the reflected light from those portions is not effectively utilized for displaying.

[0009] FIG. 16 is a diagram showing a relationship between the tilt of the reflection surface 112 and reflected light. FIG. 16(a) shows a relationship between an incident angle α and an outgoing angle β when light enters a medium b having a refractive index N_b from a medium a having a refractive index N_a . In this case, according to Snell's Law, the following relationship holds true.

$$N_a \times \sin \alpha = N_b \times \sin \beta$$

[0010] FIG. 16(b) is a diagram showing a relationship between incident light and reflected light when incident light perpendicularly entering the display surface of an LCD is reflected from a reflection surface which is tilted by θ with respect to the display surface (or the substrate). As shown in the figure, the incident light perpendicularly entering the display surface is reflected from the reflection surface which is tilted by angle θ with respect to the display surface, and goes out in a direction of an outgoing angle φ .

[0011] According to Snell's Law, results of calculating the outgoing angle φ according to Snell's Law with respect to each angle θ of the reflection surface are shown in Table 1.

[0012]

[Table 1]

θ	φ	$90-\varphi$
0	0	90
2	6.006121	83.99388
4	12.04967	77.95033
6	18.17181	71.82819
8	24.42212	65.57788
10	30.86588	59.13412
12	37.59709	52.40291
14	44.76554	45.23446
16	52.64382	37.35618
18	61.84543	28.15457
20	74.61857	15.38143
20.5	79.76542	10.23458
20.6	81.12757	8.872432
20.7	82.73315	7.266848
20.8	84.80311	5.19888
20.9	88.85036	1.149637
20.905	89.79914	0.200856

[0013] The values in this Table are calculated by assuming that air has a refractive index of 1.0 and the glass substrate and the liquid crystal layer have a refractive index of 1.5. As shown in Table 1, when the angle θ of the reflection surface exceeds 20 degrees, the outgoing angle φ becomes very large (i.e., $90-\varphi$ becomes very small), so that most of the outgoing light does not reach the user. Therefore, even if recesses/protrusions are provided on the reflection surface of the reflective layer, it is necessary to ensure that the angle θ is 20 degrees or less in greater portions of the reflection surface in order to effectively use the reflected light.

[0014] Since the reflection surface **112** of the aforementioned active matrix substrate **100** has many portions in which the angle with respect to the display surface is greater than 20 degrees, reflected light is not very effectively used for displaying. In order to solve this problem, it might be possible to form an insulating layer under the reflective layer **110** so as to cover the metal layer **108**, thus smoothing the reflection surface. However, this requires a step of forming an insulating layer, a step of forming contact holes for connecting the reflective layer **110** to the drains of TFTs in the insulating layer are need-

ed, etc., thus resulting in a problem of an increase in the material and the number of steps.

[0015] In the manufacture of the conventional active matrix substrate **100**, the gate layer **102**, the gate insulating layer **104**, a semiconductor layer **106** and the metal layer **108** are formed concurrently with and under the same conditions as the gate of the TFT, the insulating layer, the semiconductor layer and the source/drain electrode, respectively, and are thereafter etched together, and it is thus difficult to control the slope tilt, etc., of each layer. Therefore, it is difficult to give an intended tilt to the surface of the reflective layer so as to improve the reflection efficiency. Furthermore, if the width of the island-like multilayer structure is relatively large, there is formed a flat reflective layer **110** without recesses/protrusions on the multilayer structure, thereby lowering the efficiency in utilizing the reflected light.

[0016] The present invention has been made in view of the above problems, and an objective thereof is to provide a reflection-type liquid crystal display device and a transmissive-type liquid crystal display device having a high image quality and including a reflection region having a high reflectivity.

25 MEANS FOR SOLVING THE PROBLEMS

[0017] A liquid crystal display device of the present invention is a liquid crystal display device according to claim 1.

[0018] In one embodiment, the shortest distance between edge portions of at least two recesses is 1 μm or more. In one embodiment, a maximum width of at least one of the plurality of recesses is 15 μm or less. In one embodiment, the maximum width of at least one recess is 2 μm or more. In one embodiment, a shortest distance between an edge portion of any one of the plurality of recesses and an edge portion of another recess located closest thereto is 4 μm or less.

[0019] Another liquid crystal display device representing background art useful for understanding of the present invention is a liquid crystal display device comprising a reflection region for reflecting incident light toward a display surface, wherein the reflection region includes a metal layer, an insulating layer formed on the metal layer, a semiconductor layer formed on the insulating layer, and a reflective layer formed on the semiconductor layer; a plurality of protrusions are formed in at least one of the metal layer, the insulating layer and the semiconductor layer; a plurality of projections are formed in the reflective layer in the reflection region according to the plurality of protrusions; and a maximum width of at least one of the plurality of protrusions is 5 μm or less.

[0020] In one example, the maximum width of at least one protrusion is 2 μm or more. In one example, a shortest distance between edge portions of at least two of the plurality of protrusions is 15 μm or less. In one example, the shortest distance between edge portions of at least

two protrusions is 3 μm or more. In one example, a shortest distance between an edge portion of any one of the plurality of protrusions and an edge portion of another protrusion located closest thereto is 15 μm or less.

[0021] A method for manufacturing a liquid crystal display device of the present invention is a method for manufacturing a liquid crystal display device according to claim 6.

[0022] In one embodiment, the shortest distance between edge portions of at least two recesses is 1 μm or more. In one embodiment, a maximum width of at least one of the plurality of recesses is 15 μm or less. In one embodiment, the maximum width of at least one recess is 2 μm or more. In one embodiment, a shortest distance between an edge portion of any one of the plurality of recesses and an edge portion of another recess located closest thereto is 4 μm or less.

[0023] In one embodiment, in the step of forming a metal layer, photolithography technique is used to form the plurality of recesses in the metal layer and form at least one of a gate bus line and a storage capacitor line; and a thickness of a resist film used for forming the plurality of recesses is smaller than that of a resist film used for forming at least one of the gate bus line and the storage capacitor line.

[0024] Another method for manufacturing a liquid crystal display device representing background art useful for understanding of the present invention is a method for manufacturing a liquid crystal display device having a reflection region for reflecting incident light toward a display surface, comprising: a step of forming a metal layer on a substrate; a step of forming an insulating layer on the metal layer; a step of forming a semiconductor layer on the insulating layer; and a step of forming a reflective layer on the semiconductor layer, wherein a plurality of protrusions are formed in at least one of the metal layer, the insulating layer and the semiconductor layer; in the step of forming a reflective layer, a plurality of projections are formed in the reflective layer in the reflection region according to the plurality of protrusions; and a maximum width of at least one of the plurality of protrusions is 5 μm or less.

[0025] In one example, the maximum width of at least one protrusion is 2 μm or more. In one example, a shortest distance between edge portions of at least two of the plurality of protrusions is 15 μm or less. In one example, the shortest distance between edge portions of at least two protrusions is 3 μm or more. In one example, a shortest distance between an edge portion of any one of the plurality of protrusions and an edge portion of another protrusion located closest thereto is 15 μm or less.

[0026] In one example, in the step of forming a metal layer, photolithography technique is used to form the plurality of protrusions in the metal layer and form at least one of a gate bus line and a storage capacitor line; and a thickness of a resist film used for forming the plurality of protrusions is smaller than that of a resist film used for forming at least one of the gate bus line and the storage

capacitor line.

[0027] Another liquid crystal display device representing background art useful for understanding of the present invention is a liquid crystal display device comprising a reflection region for reflecting incident light toward a display surface, wherein the reflection region includes a metal layer, an insulating layer formed on the metal layer, a reflective layer formed on the insulating layer; a plurality of recesses are formed in at least one of the metal layer and the insulating layer; a plurality of dents are formed in the reflective layer in the reflection region according to the plurality of recesses; and a shortest distance between edge portions of at least two of the plurality of recesses is 4 μm or less.

[0028] Another liquid crystal display device representing background art useful for understanding of the present invention is a liquid crystal display device comprising a reflection region for reflecting incident light toward a display surface, wherein the reflection region includes a metal layer, an insulating layer formed on the metal layer, a reflective layer formed on the insulating layer; a plurality of protrusions are formed in at least one of the metal layer and the insulating layer; a plurality of projections are formed in the reflective layer in the reflection region according to the plurality of protrusions; and a maximum width of at least one of the plurality of protrusions is 5 μm or less.

[0029] Another method for manufacturing a liquid crystal display device representing background art useful for understanding of the present invention is a method for manufacturing a liquid crystal display device having a reflection region for reflecting incident light toward a display surface, comprising: a step of forming a metal layer on a substrate; a step of forming an insulating layer on the metal layer; and a step of forming a reflective layer on the insulating layer, wherein a plurality of recesses are formed in at least one of the metal layer and the insulating layer; in the step of forming a reflective layer, a plurality of dents are formed in the reflective layer in the reflection region according to the plurality of recesses; and a shortest distance between edge portions of at least two of the plurality of recesses is 4 μm or less.

[0030] Another method for manufacturing a liquid crystal display device representing background art useful for understanding of the present invention is a method for manufacturing a liquid crystal display device having a reflection region for reflecting incident light toward a display surface, comprising: a step of forming a metal layer on a substrate; a step of forming an insulating layer on the metal layer; and a step of forming a reflective layer on the insulating layer, wherein a plurality of protrusions are formed in at least one of the metal layer and the insulating layer; in the step of forming a reflective layer, a plurality of projections are formed in the reflective layer in the reflection region according to the plurality of protrusions; and a maximum width of at least one of the plurality of protrusions is 5 μm or less.

EFFECTS OF THE INVENTION

[0031] According to the present invention, it is possible to provide a reflection-type liquid crystal display device and a transfective-type liquid crystal display device having a high image quality and including a reflection region having a high reflectivity.

BRIEF DESCRIPTION OF DRAWINGS

[0032]

[FIG. 1] A diagram schematically showing a cross-sectional shape of the liquid crystal display device according to Embodiment 1 of the present invention.

[FIG. 2] Diagrams specifically illustrating the construction of a pixel region and a reflection section of Embodiment 1, where (a) is a plan view showing a portion of a pixel region as viewed from above the display surface, and (b) is a plan view schematically showing the construction of a reflection section of a liquid crystal display device.

[FIG. 3] Cross-sectional views showing the construction of a reflection section and a TFT section of Embodiment 1, where (a) shows the construction of a reflection section, and (b) shows the construction of a TFT section.

[FIG. 4] Plan views showing a method for manufacturing a TFT section of Embodiment 1.

[FIG. 5] Cross-sectional views showing a method for manufacturing a TFT section of Embodiment 1.

[FIG. 6] Plan views showing a method for manufacturing a reflection section of Embodiment 1.

[FIG. 7] Cross-sectional views showing a method for manufacturing a reflection section of Embodiment 1.

[FIG. 8] Cross-sectional views showing a method for shaping a gate line, a gate electrode, a Cs line and a Cs metal layer of Embodiment 1.

[FIG. 9] Diagrams showing examples of shapes and arrangements of recesses 57 of Embodiment 1.

[FIG. 10] A cross-sectional view showing the construction of a reflection section of Embodiment 2.

[FIG. 11] Diagrams showing examples of shapes and arrangements of protrusions 169 of Embodiment 2.

[FIG. 12] A cross-sectional view showing the construction of a reflection section of Embodiment 3.

[FIG. 13] Schematic diagrams for comparison between the construction of a reflection section of Embodiment 3 and that of a conventional liquid crystal display device, where (a) shows a cross section of the reflection section, (b) shows a cross section of the reflection section of the conventional liquid crystal display device, and (c) shows surface angles at a corner portion of the reflection section.

[FIG. 14] A cross-sectional view showing a liquid crystal display device of Embodiment 4.

[FIG. 15] A cross-sectional view showing an active matrix substrate in a conventional reflection-type

LCD.

[FIG. 16] Diagrams showing a relationship between a tilt of a reflection surface and reflected light in a liquid crystal display device, where (a) shows a relationship between an incident angle α and an outgoing angle β when light enters a medium b having a refractive index N_b from a medium a having a refractive index N_a , and (b) shows a relationship between incident light and reflected light as well as the angle of the display surface of the LCD.

DESCRIPTION OF THE REFERENCE NUMERALS

[0033]

10	liquid crystal display device
12	TFT substrate
14	counter substrate
16	liquid crystal
18	liquid crystal layer
22	transparent substrate
26	interlayer insulating layer
28	pixel electrode
30	reflection section
31	layer
32	TFT section
34	counter electrode
36	CF layer
38	transparent substrate
40	display surface
42	reflection region
44	TFT region
46	transmission region
48	recess
48'	protrusion
50	pixel
52	source line

54	gate line
56	Cs line
57	recess
58	contact hole
61	gate insulating layer
62	semiconductor layer
63	reflective layer
67	slope
69	protrusion
69'	upper portion
70	lower portion
85	upper slope
86	flat portion
87	lower slope
90	slope
91, 92	recess
99	photoresist
148, 157	recess
169	protrusion

BEST MODE FOR CARRYING OUT THE INVENTION

(Embodiment 1)

[0034] Hereinafter, with reference to the drawing, a first embodiment of the liquid crystal display device according to the present invention will be described.

[0035] FIG. 1 schematically shows a cross-sectional structure of a liquid crystal display device 10 of the present embodiment. The liquid crystal display device 10 of the present embodiment is a transfective-type liquid crystal display device by an active matrix method. As shown in FIG. 1, the liquid crystal display device 10 includes a TFT (Thin Film Transistor) substrate 12, a counter substrate 14, and a liquid crystal layer 18 containing liquid crystal 16 which is sealed between the TFT substrate 12 and the counter substrate 14.

[0036] The TFT substrate 12 comprises a transparent substrate 22, an interlayer insulating layer 26, and a pixel electrode 28, and includes reflection sections 30 and TFT

sections 32. Gate lines (scanning lines), source lines (signal lines), and Cs lines (storage capacitor electrode lines), etc., are formed on the TFT substrate 12, which will be described later.

5 **[0037]** The counter substrate 14 is a color filter substrate (CF substrate), for example, and includes a counter electrode 34, a color filter layer (CF layer) 36, and a transparent substrate 38. The upper face of the transparent substrate 38 serves as a display surface 40 of the liquid crystal display device. Note that although the TFT substrate 12 and the counter substrate 14 each have an alignment film and a polarizer, they are omitted from the figure.

10 **[0038]** In the liquid crystal display device 10, a region where a reflection section 30 is formed is referred to as a reflection region 42, whereas a region where a TFT section 32 is formed is referred to as a TFT region 44. In the reflection region 42, light entering from the display surface 40 is reflected by the reflection section 30, and travels through the liquid crystal layer 18 and the counter substrate 14 so as to go out from the display surface 40. The liquid crystal display device 10 further has transmission regions 46 which are formed in regions other than the reflection regions 42 and the TFT regions 44. In the transmission regions 46, light which is emitted from a light source in the display device 10 travels through the TFT substrate 12, the liquid crystal layer 18, and the counter substrate 14 so as to go out from the display surface 40.

20 **[0039]** Note that, as shown in FIG. 1, a layer 31 which is composed of a transmissive resin or the like is provided at the counter substrate 14 side above each reflection section 30, and the thickness of the liquid crystal layer 18 in the reflection region 42 is a half of the thickness of the liquid crystal layer 18 in the transmission region 46. As a result, the optical path length (the distance over which light travels through the liquid crystal layer 18) in the reflection region 42 and that in the transmission region 46 are equal to each other. Although FIG. 1 illustrates the layer 31 as being formed between the counter electrode 34 and the CF layer 36, the layer 31 may be formed on the face of the counter electrode 34 facing the liquid crystal layer 18.

25 **[0040]** FIG. 2 is a plan view more specifically showing the construction of the pixel region and the reflection section 30 in the liquid crystal display device 10.

30 **[0041]** FIG. 2(a) is a plan view of a portion of a pixel region of the liquid crystal display device 10, as seen from above the display surface 40. As shown in the figure, a plurality of pixels 50 (rectangular portions denoted by bold lines) are provided in a matrix shape on the liquid crystal display device 10. The aforementioned reflection section 30 and TFT section 32 are formed in each pixel 50.

35 **[0042]** In the border of the pixel 50, source lines 52 extend along the column direction (the vertical direction in the figure), and gate lines (gate metal layers) 54 extend along the row direction (the horizontal direction in the

figure). In the central portion of the pixel 50, a Cs line (Cs metal layer) 56 extends along the row direction. In the interlayer insulating layer 26 of the reflection section 30, a contact hole 58 for connecting the pixel electrode 28 and the drain electrode of the TFT is formed. The Cs line 56, paired with the pixel electrode, forms a storage capacitor.

[0043] FIG. 2(b) is a plan view schematically showing the construction of the reflection section 30 above the Cs line 56. The contact hole 58 shown in FIG. 2(a) is omitted from this figure. As shown in the figure, a plurality of circular recesses (dents) 48 are formed in the reflection section 30. As will be described later, a reflective layer is formed in an upper portion of the reflection section 30, and the surface of the recesses 48 is formed as the surface of the reflective layer. The reflective layer is connected to the drain electrode of the TFT in the TFT section 32. Thus, by forming many recesses 48 in the reflection section 30, the angle θ can be made 20 degrees or less in greater portions of the reflection surface. Therefore, it is possible to improve the reflection efficiency in the reflection section.

[0044] Although only eight recesses 48 are shown in the figure for a better understanding of the construction, the number of the recesses 48 is not limited to eight, but there may be more recesses 48. The recesses 48 do not have to be arranged regularly in the vertical and horizontal direction as shown in the figure, but may be arranged randomly or with irregular spacing. According to the present embodiment, many recesses 48 can be formed as closely together as possible by a method to be described later.

[0045] Next, referring to FIG. 3, the construction of the reflection section 30 and the TFT section 32 will be described in greater detail.

[0046] FIG. 3(a) shows a cross section of the reflection section 30 (a cross section of a portion shown by arrow C in FIG. 2(b)). As shown in the figure, the Cs metal layer (metal layer) 56, a gate insulating layer 61, a semiconductor layer 62, and a reflective layer 63 are stacked in the reflection section 30. The semiconductor layer 62 includes an intrinsic amorphous silicon layer (Si(i) layer), and an n⁺ amorphous silicon layer (Si(n⁺) layer) doped with phosphorus.

[0047] The Cs metal layer 56 in the reflection section 30 includes recesses (or openings) 57 formed therein as shown in the figure, and protrusions 69 of the Cs metal layer 56 are formed between the recesses 57. The recesses 48 of the reflective layer 63 are formed according to the shape of the recesses 57 of the Cs metal layer 56. The semiconductor layer 62 may possibly be absent in the reflection section 30.

[0048] FIG. 3(b) is a cross-sectional view showing the construction of the gate metal layer (metal layer) 54, the gate insulating layer 61, the semiconductor layer 62, and the reflective layer 63 in the TFT section 32. The gate metal layer 54 in the TFT section 32 is formed concurrently with and from the same member as the Cs metal

layer 56 of the reflection section 30. Similarly, the gate insulating layer 61, the semiconductor layer 62, and the reflective layer 63 of the TFT section 32 are formed concurrently with and from the same members as the gate insulating layer 61, the semiconductor layer 62, and the reflective layer 63 of the reflection section 30, respectively.

[0049] In FIG. 3(a), a denotes the interval between two recesses 57 of the Cs metal layer 56. In the present embodiment, the interval a between the recesses 57 means the shortest distance between edge portions of two adjacent recesses 57 (the recess edges at the upper surface of the Cs metal layer 56). In order to enhance the reflection efficiency in the reflection section 30, it is better to provide more recesses 48 on the surface of the reflective layer 63. This is because it is then possible to form more surfaces where the tilt is 20 degrees or less on the surface of the reflective layer 63. For this, it is necessary to provide more recesses 57 also in the Cs metal layer 56. Thus, in the present embodiment, the interval a is set to 4 μm or less, and the maximum width b of the recess 57 (the maximum width of the opening on the upper surface of the Cs metal layer 56) is set to 15 μm or less. The lower limit of the interval a is set to 1 μm in view of the limitations of the manufacture process, and the lower limit of the width b is set to 2 μm for the same reason. That is, a preferred predetermined range of the interval a is 1 μm or more and 4 μm or less, and the predetermined range of the width b is 2 μm or more and 15 μm or less.

[0050] In order to improve the reflection efficiency, it is preferred that the interval a between any two recesses 57 adjacent to each other is within the aforementioned predetermined range. Nevertheless, the present invention is not limited to this, and the reflection efficiency can also be improved by setting the interval a between a recess 57 and another recess 57 located closest thereto to a value within the predetermined range. The reflection efficiency can also be improved by setting the interval a between a recess and another recess located closest thereto to a value within the predetermined range for 50% or more of the recesses 57 formed in the reflection section 30. The reflection efficiency can also be improved by setting the interval a between at least two recesses 57 in the reflection section 30 to a value within the predetermined range.

[0051] In order to improve the reflection efficiency, it is preferred that the width b of all the recesses 57 is within the aforementioned predetermined range. Nevertheless, the present invention is not limited to this, and the reflection efficiency can also be improved by setting the width b within the predetermined range for 50% or more of the recesses 57 formed in the reflection section 30. The reflection efficiency can also be improved by setting the width b to a value within the predetermined range for at least one recess 57 in the reflection section 30.

[0052] In the conventional liquid crystal display device shown in FIG. 15, recesses are formed in portions where

the gate layer **102**, the gate insulating layer **104** and the semiconductor layer **106** have been removed, and the bottom surfaces of the recesses are therefore formed at deep positions. Therefore, the inner surface of each recess has a large tilt angle, thus making it difficult to form within the recess a large number of effective reflection surfaces having a tilt of 20 degrees or less. Moreover, these recesses are formed by forming the gate layer **102**, the gate insulating layer **104**, and the semiconductor layer **106**, and then removing these layers altogether. Thus, it is not possible to control the shape of the inner surface of each recess and the tilt angle of the slope, making it difficult to increase the effective reflection surfaces.

[0053] According to the present embodiment, the recesses **48** (dents) of the reflective layer **63** are formed according to the controlled shape of the Cs metal layer **56**, and it is therefore possible to easily form relatively shallow dents in the reflective layer. Therefore, the reflection efficiency at the surface of the reflective layer is improved. Since the shape, the depth, the slope tilt angle, etc., of the recesses **48** can easily be adjusted, the recesses **48** of the reflective layer **63** can easily be formed with a slope tilt angle of 20 degrees or less. Therefore, it is possible to increase the area of the effective reflection surface without increasing the manufacturing cost.

[0054] According to the present embodiment, the interval between the recesses **57** in the Cs metal layer **56** can be set to be as small as practically possible. The width of the recesses **57** themselves can also be made as small as possible. Then, more recesses **57** of the Cs metal layer **56** can be arranged in the reflection section **30**, thus forming more recesses **48** in the reflective layer **63**. This increases the area of the surface where the tilt is 20 degrees or less on the surface of the reflective layer **63**, thereby improving the reflection efficiency. Furthermore, since it is possible to reduce the area of the flat portion of the surface of the reflective layer **63**, it is possible to further improve the reflection efficiency.

[0055] Next, a method for manufacturing the TFT substrate **12** according to the present embodiment will be described.

[0056] FIG. 4 is plan views showing a method for manufacturing the TFT substrate **12** in the TFT section **32**. FIG. 5 is cross-sectional views showing a method for manufacturing the TFT substrate **12** in the TFT section **32**, showing a cross section of a portion shown by arrow **A** in FIG. 2(a).

[0057] As shown in FIG. 4(a) and FIG. 5(a), first, by a method such as sputtering, a thin metal film of Al (aluminum) is formed on the transparent substrate **22** having been cleaned. Note that, other than Al, this thin metal film may be formed by using Ti (titanium), Cr (chromium), Mo (molybdenum), Ta (tantalum), W (tungsten), or an alloy thereof, etc., or formed from a multilayer body of a layer of such materials and a nitride film.

[0058] Thereafter, a resist film is formed on the thin metal film, and after forming a resist pattern through an exposure and development step, a dry or wet etching is

performed to form the gate metal layer **54** (including the gate electrode and the gate line). The gate metal layer **54** has a thickness of 200 to 500 nm, for example.

[0059] Thus, the gate metal layer **54** which is formed by photolithography technique serves as a gate electrode of the TFT. Note that, in this step, the gate lines (gate metal layer) **54** shown in FIG. 2(a) and the Cs metal layer **56** of the reflection section **30** shown in FIG. 3(a) are also formed from the same metal concurrently.

[0060] Next, as shown in FIG. 4(b) and FIG. 5(b), by using P-CVD technique and a gaseous mixture of SiH_4 , NH_3 , and N_2 , the gate insulating layer **61** composed of SiN (silicon nitride) is formed across the entire substrate surface. The gate insulating layer **61** may also be composed of SiO_2 (silicon oxide), Ta_2O_5 (tantalum oxide), Al_2O_3 (aluminum oxide), or the like. The thickness of the gate insulating layer **61** is 300 to 500 nm, for example. In this step, the gate insulating layer **61** of the reflection section **30** shown in FIG. 3(a) is also formed concurrently.

[0061] Next, on the gate insulating layer **61**, an amorphous silicon (a-Si) (Si(i) film) film and an n⁺a-Si film (Si (n⁺) film) obtained by doping amorphous silicon with phosphorus (P). The thickness of the a-Si film is 30 to 300 nm, for example, and the thickness of the n⁺a-Si film is 20 to 100 nm, for example. Thereafter, these films are shaped by photolithography technique, whereby the semiconductor layer **62** is formed. In this step, the semiconductor layer **62** of the reflection section **30** shown in FIG. 3(a) is also formed concurrently.

[0062] Next, as shown in FIG. 4(c) and FIG. 5(c), a thin metal film of Al or the like is formed across the entire substrate surface by sputtering technique or the like, and a photolithography technique is performed to form the reflective layer **63**. For the thin metal film, the materials which are mentioned above as materials for the gate metal layer **54** may be used. The thickness of the reflective layer **63** is 30 to 1000 nm, for example. In the TFT section **32**, the reflective layer **63** forms a source electrode and a drain electrode of the TFT. At this time, the source line **52** in FIG. 2(a) is also formed as a portion of the reflective layer **63**, and the reflective layer **63** of the reflection section **30** shown in FIG. 3(a) is also formed concurrently.

[0063] Next, as shown in FIG. 4(d) and FIG. 5(d), a photosensitive acrylic resin is applied by spin-coating, whereby the interlayer insulating layer (interlayer resin layer) **26** is formed. The thickness of the interlayer insulating layer **26** is 0.3 to 5 μm , for example. Although a thin film such as SiN_x or SiO_2 may be formed by P-CVD technique as a protection film between the reflective layer **63** and the interlayer insulating layer **26**, such is omitted from the figure. The thickness of the protection film is 50 to 1000 nm, for example. The interlayer insulating layer **26** and the protection film are formed not only on the TFT section **32**, but also on the entire upper surface of the transparent substrate **22** including the reflection section **30**.

[0064] Next, as shown in FIG. 4(e) and FIG. 5(e), on the interlayer insulating layer **26**, a transparent electrode

film such as ITO or IZO is formed by sputtering technique or the like. This transparent electrode film is pattern shaped by photolithography technique, whereby the pixel electrode **28** is formed. The pixel electrode **28** is formed not only on the TFT section **32** but also on the entire upper surface of the pixel including the reflection section **30**.

[0065] Next, by using FIG. **6** and FIG. **9**, a method for manufacturing the TFT substrate **12** in the reflection section **30** will be described.

[0066] FIG. **6** is a plan view showing a method for manufacturing the TFT substrate **12** in the reflection section **30**. FIG. **7** is a cross-sectional view showing a method for manufacturing the TFT substrate **12** in the reflection section **30**, showing a cross section of a portion shown by arrow **C** in FIG. **2(b)**. The steps shown at (a) to (e) in FIG. **6** and FIG. **7** correspond to the steps of (a) to (e) in FIG. **4** and FIG. **5**, respectively.

[0067] As shown in FIG. **6(a)** and FIG. **7(a)**, the Cs metal layer **56** in the reflection section **30** is formed, by a similar method, concurrently with and from the same metal as the gate metal layer **54** in the TFT section **32**. When the thin metal film is shaped by photolithography technique, a plurality of recesses **57** are formed in the Cs metal layer **56** according to the openings of the photoresist so that the interval **a** between two recesses **57** and the width **b** of each recess **57** are within the aforementioned predetermined ranges. A more specific method for forming the recesses **57** will be described later.

[0068] Next, as shown in FIG. **6(b)** and FIG. **7(b)**, the gate insulating layer **61** is formed by a method similar to that for the TFT section **32**, and thereafter the semiconductor layer **62** is formed. While the semiconductor layer **62** is formed in the TFT section **32**, the semiconductor layer **62** may possibly be absent in the reflection section **30** by, for example, removing the semiconductor material in the patterning process.

[0069] Next, As shown in FIG. **6(c)** and FIG. **7(c)**, the reflective layer **63** is formed on the semiconductor layer **62** (on the gate insulating layer **61** if the semiconductor layer **62** is not formed) by a method similar to that for the TFT section **32**. On the surface of the reflective layer **63**, the recesses **48** are formed, reflecting the recesses **57** and the protrusions **69** of the Cs metal layer **56**.

[0070] Next, as shown in FIG. **6(d)** and FIG. **7(d)**, the interlayer insulating layer **26** is formed from photosensitive acrylic resin. Thereafter, through a development process using an exposure apparatus, the contact hole **58** is formed near the center of the reflection section **30**.

[0071] Next, as shown in FIG. **6(e)** and FIG. **7(e)**, the pixel electrode **28** is formed. In the reflection section **30**, the pixel electrode **28** is formed above the interlayer insulating layer **26** and the contact hole **58**, such that the metal member of the pixel electrode **28** is in contact with the reflective layer **63** via the contact hole **58**. As a result, the drain electrode of the TFT in the TFT section **32** is electrically connected with the pixel electrode **28** via the contact hole **58**.

[0072] Next, using FIG. **8**, a method for manufacturing the Cs metal layer **56** of the present embodiment, the gate line (gate bus line) **54**, and the gate electrode in the TFT section will be described in greater detail.

[0073] FIG. **8(a)** is a diagram showing the shape of a photoresist **99** used when forming the gate line **54**, showing the cross-sectional shape at the position shown by arrow **B** in FIG. **2(a)**. FIG. **8(b)** is a diagram showing the shape of the photoresist **99** used when forming the Cs metal layer **56** in the reflection section **30**, showing the cross-sectional shape at the position shown by arrow **D** in FIG. **2(c)**.

[0074] As described above, when forming the Cs metal layer **56**, the gate electrode and the gate line **54** in the TFT section **32** are also formed concurrently and from the same metal by photolithography technique. While a photoresist having a height **x** is used as shown in FIG. **8(a)** when shaping the gate line (and the gate electrode) **54**, a photoresist having a height **y** shallower than **x** is used when shaping the Cs metal layer **56** in the reflection section **30**. The photoresist is uniformly deposited with the height **x** across the substrate surface including the TFT section **32** and the reflection section **30**, and then exposure conditions and baking conditions, for example, are appropriately set in the reflection section **30** so that the film has the height **y** at its top.

[0075] Thus, since the thickness of the resist film used in the formation of the recesses **57** is thinner than that of the resist film used in the formation of the gate line **54**, a gentle slope is formed at the edge portion of the recess **57** in the film-shaping process by etching, whereas a steep slope is formed at the edge portion of the gate line **54**. As shown in FIG. **8(b)**, for the Cs metal layer **56** outside the reflection section **30**, the photoresist **99** having the height **x** is used, and therefore the slope at the edge portion of the Cs line **56** is also a steep slope.

[0076] Using such a method, it is readily possible, by the same photolithography step, to form the recess **57** with a gentle slope of 20° or less, for example, and to shape the gate line **54** and the Cs line **56** with a high process precision. Moreover, since it is possible to easily control the size, shape and slope tilt of the recesses **57** and the interval between the recesses **57**, it is possible to obtain intended recesses **57** without increasing the number of steps. Thus, it is possible to efficiently manufacture a liquid crystal display device having a high reflectivity in which the reflective layer **63** has many surfaces where the tilt is 20° or less.

[0077] Next, using FIG. **9**, a variation of the shape and the arrangement method of the recesses **57** will be described.

[0078] (a) to (e) of FIG. **9** each show an example of the edge shape and the arrangement of the recesses **57** as viewed in a direction vertical to the substrate surface. The recesses **57** may be formed in a circular shape as shown in (a) to (c) and (e) of FIG. **9**, or in a hexagonal shape as shown in FIG. **9(d)**. The shape of the recess **57** is not limited to those illustrated herein, but elliptic

shapes, polygonal shapes, or other shapes, may be used. The arrangement of the recesses **57** may be a regular arrangement as shown in FIGS. **9(a)** to **(d)**, or may be an irregular or random arrangement as shown in FIG. **9(e)**. In any case, the interval **a** between the recesses **57** is defined as the shortest distance between the edge portions of two adjacent recesses **57**, and the width **b** of a recess **57** is defined as the maximum width between edge portions of the recess **57**.

[0079] Although the recesses **57** are described as being formed in the Cs metal layer (metal layer) **56** in the embodiment above, the recesses **57** may be formed in the gate insulating layer **61** or the semiconductor layer **62** in the reflection section **30**, or may be formed in two or all of these layers. Furthermore, the recesses **57** may be provided in one or two of these layers, with protrusions as will be described in Embodiment 2 being formed in one or two other layers thereof. The semiconductor layer **62** may be absent in the reflection section **30**. The recesses **57** may be formed by the aforementioned photolithography technique, or the like, during the formation of the layers. The embodiments of the present invention are deemed to encompass these examples.

(Embodiment 2)

[0080] Next, using FIGS. **10** and **11**, a second embodiment of the liquid crystal display device of the present invention will be described. The second embodiment is directed to the liquid crystal display device **10** shown in FIG. **1**, except that the reflection section **30** shown in FIG. **3(a)** is replaced by that shown in FIG. **10**. Otherwise, the construction is the same as that of Embodiment 1, and only what are different from Embodiment 1 will be described. Like elements to those of Embodiment 1 will be denoted by like reference numerals and will not be described below.

[0081] FIG. **10** shows a cross section of the reflection section **30** of Embodiment 2 (a cross section of a portion shown by arrow C in FIG. **2(b)**). In the reflection section **30** shown in FIG. **10**, the recess **48** shown in FIG. **2(b)** corresponds to a protrusion (projection) **48'**. That is, the recess/protrusion pattern on the surface of the reflection section **30** in Embodiment 1 is reversed from that of Embodiment 2 so that the recess **48** shown as a circular recess in FIG. **3(a)** is the protrusion **48'** in Embodiment 2.

[0082] A plurality of protrusions **169** are formed in the Cs metal layer **56** in the reflection section **30** as shown in the figure, and a recess **157** of the Cs metal layer **56** is formed between two protrusions **169**. The protrusion **48'** of the reflective layer **63** is formed according to the shape of the protrusion **169** of the Cs metal layer **56**.

[0083] In FIG. **10**, **c** denotes the width of the protrusion **169**. The maximum width **c** means the maximum width of the protrusion **169** at the bottom surface of the Cs metal layer **56**. Moreover, **d** denotes the interval between two protrusions **169** of the Cs metal layer **56**. The interval **d** denotes the shortest distance between edge portions

of two adjacent protrusions **169** (the edges of the protrusions **169** at the lower surface of the Cs metal layer **56**). In order to enhance the reflection efficiency in the reflection section **30**, it is better to provide more protrusions **48'** and recesses **148** on the surface of the reflective layer **63**. This is because it is then possible to form more surfaces where the tilt is 20 degrees or less on the surface of the reflective layer **63**. For this, it is necessary to provide more protrusions **169** and recesses **157** also in the Cs metal layer **56**. Thus, in the present embodiment, the width **c** of the protrusion **169** is set to 5 μm or less, and the interval **d** is set to 15 μm or less. The lower limit of the width **c** is set to 2 μm in view of the limitations of the manufacture process, and the lower limit of the interval **d** is set to 2 μm for the same reason. That is, a preferred predetermined range of the width **c** is 2 μm or more and 5 μm or less, and the predetermined range of the interval **d** is 2 μm or more and 15 μm or less.

[0084] In order to improve the reflection efficiency, it is preferred that the interval **d** between any two protrusions **169** adjacent to each other is within the aforementioned predetermined range. Nevertheless, the present invention is not limited to this, and the reflection efficiency can also be improved by setting the interval **d** between a protrusion **169** and another protrusion **169** located closest thereto to a value within the predetermined range. The reflection efficiency can also be improved by setting the interval **d** between a protrusion and another protrusion located closest thereto to a value within the aforementioned predetermined range for 50% or more of the protrusions **169** formed in the reflection section **30**. The reflection efficiency can also be improved by setting the interval **d** between at least two protrusions **169** in the reflection section **30** to a value within the predetermined range.

[0085] In order to improve the reflection efficiency, it is preferred that the width **c** of all the protrusions **169** is within the aforementioned predetermined range. Nevertheless, the present invention is not limited to this, and the reflection efficiency can also be improved by setting the width **c** within the aforementioned predetermined range for 50% or more of the protrusions **169** formed in the reflection section **30**. The reflection efficiency can also be improved by setting the width **c** to a value within the predetermined range for at least one protrusion **169** in the reflection section **30**.

[0086] The aforementioned Cs metal layer **56** can be formed by a method similar to that described in Embodiment 1. Note however that when shaping the Cs metal layer **56**, a mask having a pattern obtained by inverting the pattern used in Embodiment 1 is used as a resist mask. Therefore, the recesses **57** are formed by a so-called "negative-type pattern" in Embodiment 1, whereas the protrusions **169** are formed by a "positive-type pattern" in Embodiment 2.

[0087] Next, using FIG. **11**, a variation of the shape and the arrangement of the protrusions **169** will be described.

[0088] (a) to (f) of FIG. 11 each show an example of the edge shape and the arrangement of the protrusions 169 as viewed in a direction vertical to the substrate surface. The protrusions 169 may be formed in a circular shape as shown in (a) and (c) of FIG. 11, or may be formed in a hexagonal shape as shown in (b). Moreover, the protrusion 169 may be in a circular shape or a hexagonal shape having a recess therein as shown in (d) and (e), or may be in a cross shape as shown in (f). The shape of the protrusion 169 is not limited to those illustrated herein, but elliptic shapes, polygonal shape shapes, or other shapes, may be used. The arrangement of the protrusions 169 may be a regular arrangement as shown in (a) and (b), or may be an irregular or random arrangement as shown in (c). In any case, the width **c** of a protrusion 169 is defined as the maximum width of the protrusion 169, and the interval **d** is defined as the shortest distance between the edge portions of two adjacent protrusions 169. In a case where the protrusion 169 extends in a line pattern as shown in (d) to (f), the width **c** thereof is defined as the maximum width of the line portion.

[0089] According to the present embodiment, the protrusions 48' (projections) of the reflective layer 63 are formed according to the controlled shape of the Cs metal layer 56, and it is therefore possible to easily form relatively low projections on the reflective layer. Therefore, the reflection efficiency at the surface of the reflective layer is improved. Since the shape, the height, the slope tilt angle, etc., of the protrusions 48' can easily be adjusted, it is easy to form many slopes where the tilt angle is 20 degrees or less on the surface of the reflective layer 63. Therefore, it is possible to increase the area of the effective reflection surface without increasing the manufacturing cost.

[0090] According to the present embodiment, the width and the interval of the protrusion 169 in the Cs metal layer 56 can be set to be as small as practically possible. Then, more protrusions 169 of the Cs metal layer 56 can be arranged in the reflection section 30, thus forming more protrusions 48' in the reflective layer 63. This increases the area of the surface where the tilt is 20 degrees or less on the surface of the reflective layer 63, thereby improving the reflection efficiency. Furthermore, since it is possible to reduce the area of the flat portion of the surface of the reflective layer 63, it is possible to further improve the reflection efficiency.

[0091] Although the protrusions 169 are described as being formed in the Cs metal layer (metal layer) 56 in the embodiment above, such protrusions may be formed in the gate insulating layer 61 or the semiconductor layer 62 in the reflection section 30, or may be formed in two or all of these layers.

[0092] Furthermore, the protrusions 169 may be provided in one or two of these layers, with recesses as described in Embodiment 1 being formed in one or two other layers thereof. The semiconductor layer 62 may be absent in the reflection section 30. The protrusions 169

may be formed by the aforementioned photolithography technique, or the like, during the formation of the layers. The embodiments of the present invention are deemed to encompass these examples.

(Embodiment 3)

[0093] Next, a third embodiment of the liquid crystal display device of the present invention will be described. The third embodiment is directed to the liquid crystal display device 10 shown in FIG. 1, except that the reflection section 30 shown in FIG. 3(a) is replaced by that shown in FIG. 12. Otherwise, the construction is the same as that of Embodiment 1, and only what are different from Embodiment 1 of the reflection section 30 will be described. Like elements to those of Embodiments 1 and 2 will be denoted by like reference numerals and will not be described below.

[0094] FIG. 12 shows a cross section of the recess 48 in the reflection section 30 of Embodiment 3 (a cross section of a portion shown by arrow C in FIG. 2(b)). As shown in the figure, the Cs metal layer (metal layer) 56, the gate insulating layer 61, the semiconductor layer 62 and the reflective layer 63 are stacked in the reflection section 30.

[0095] A plurality of recesses (or openings) 57' are formed in the Cs metal layer 56 in the reflection section 30 as shown in the figure, and a protruding portion 89 of the Cs metal layer 56 is formed between the recesses 57'. A slope 67 of the protruding portion 89 is formed with a step, and the slope 67 includes an upper slope 85, a flat portion 86 and a lower slope 87. The flat portion 86 is formed generally parallel to the substrate surface. A portion of the protruding portion 89 that is above a plane that includes the flat portion 86 is referred to as an upper portion 69', and a portion below the plane is referred to as a lower portion 70. The recesses 48 of the reflective layer 63 are formed according to the shape of the recesses 57' of the Cs metal layer 56.

[0096] A reflection section 30' may be manufactured by a method similar to that described above using FIGS. 6 to 8. The interval **a** shown in Embodiment 1 is the shortest distance between edge portions of uppermost portions of two recesses 57', and the width **b** is the maximum width between edge portions of the uppermost portion of the recess 57'. One may consider that the interval **a** is the shortest distance between edge portions of the recesses 57' on a plane that includes the flat portion 86, and the width **b** is the maximum width between edge portions of the recess 57' on the same plane. The Cs metal layer 56 having a shape obtained by inverting the recess/protrusion pattern of Embodiment 3 may be used. A construction obtained by forming a step as shown in the present embodiment in the recesses and the protrusions of the Cs metal layer 56 of Embodiments 1 and 2 is also included in embodiments of the present invention. Furthermore, a construction obtained by providing recesses in one or two of the Cs metal layer 56, the gate

insulating layer **61** and the semiconductor layer **62**, and a construction obtained by providing protrusions in one or two of these layers with recesses provided in one or two other layers thereof, are also included in embodiments of the present invention. A construction where the semiconductor layer is not provided in the reflection section **30'** is also included in embodiments of the present invention.

[0097] According to the present embodiment, there is obtained an advantage as follows, in addition to those described in Embodiments 1 and 2.

[0098] FIG. **13** shows diagrams for comparison between the construction of the reflection section **30** of the present embodiment and that of the reflection section of the conventional liquid crystal display device shown in FIG. **15**. FIG. **13(a)** schematically shows a cross-sectional structure of the reflection section **30** of the present embodiment, and FIG. **13(b)** schematically shows a cross-sectional structure of the reflection section of the conventional liquid crystal display device. As shown in these figures, on the surface of the reflective layer **63** of the present embodiment, there is formed a stepped slope **90**, reflecting the slope of the protruding portion **89** of the Cs metal layer **56**. Thus, a recess **91** and a recess **92** located inside the recess **91** are formed in the reflective layer **63**. The recess **48** shown in FIG. **2(b)** is formed by the recess **91** and the recess **92**.

[0099] As seen in a cross-sectional shape, each recess **48** includes eight corner portions (portions shown by dotted lines in the figure). In the conventional liquid crystal display device, each recess includes only four corner portions as shown in FIG. **13(b)**. At the corner portions of the reflective layer, surfaces having an angle greater than 20 degrees with respect to the substrate from the plane parallel to the substrate (represented as being 30 degrees, for example, in this figure) are formed continuously as shown in FIG. **13(c)**. Therefore, if more recesses are formed in the reflection section, it is possible to form more effective reflection surfaces (surfaces whose angle with respect to the substrate is 20 degrees or less) on the surface of the reflective layer **63**.

[0100] As can be seen from FIGS. **13(a)** and **(b)**, a two-tiered recess having a step therein is formed in the reflective layer **63** of the present embodiment. Therefore, the surface of the reflective layer **63** has more corner portions than the conventional reflection section. Thus, more effective reflection surfaces are formed on the surface of the reflective layer **63**, and it is therefore possible to improve the reflection efficiency of the reflection section **30**. Since the recesses **91** and the recesses **92** are formed according to the controlled shape of the Cs metal layer **56**, the shape, the depth and the slope tilt angle of the recesses can easily be adjusted.

[0101] Although the protruding portion **89** of the Cs metal layer **56** has a two-tiered structure including the upper portion **69'** and the lower portion **70** in the present embodiment, the protruding portion **89** may be formed with three or more tiers of steps. In this case, a recess

is further formed inside the recess **92** formed in the reflective layer **63**, and it is therefore possible to obtain an even higher reflection efficiency.

[0102] In the embodiment above, the recess **91** and the recess **92** formed on the surface of the reflective layer **63** are assumed to be formed concentrically as viewed in a direction vertical to the substrate. Nevertheless, the present invention is not limited to this, and the recess **91** and the recess **92** may be arranged so that their centers are not aligned with each other. The periphery of the recess **91** and that of the recess **92** may partially overlap each other. Also in these cases, many recesses/protrusions with steps are formed on the surface of the reflective layer **63**, whereby it is possible to widen the effective reflection surface.

(Embodiment 4)

[0103] Hereinafter, with reference to the drawing, a fourth embodiment of the liquid crystal display device according to the present invention will be described. Like elements to those of Embodiments 1 to 3 will be denoted by like reference numerals and will not be described below.

[0104] FIG. **14** schematically shows a cross-sectional shape of the liquid crystal display device of the present embodiment. This liquid crystal display device is based on the liquid crystal display devices of Embodiments 1 to 3 from which the interlayer insulating layer **26** is excluded, and is identical to the liquid crystal display devices of Embodiments 1 to 3 except for the points discussed below. Note that, in FIG. **14**, the detailed structure of the counter substrate **14** and the TFT section **32** are omitted from illustration.

[0105] As shown in the figure, in the present embodiment, the interlayer insulating layer is not formed, and therefore the pixel electrode **28** is formed upon the reflective layer **63** in the reflection section **30** and in the TFT section **32**, via an insulating film not shown. The structure and the manufacturing method for the reflection section **30** and the TFT section **32** are the same as in Embodiment 1 except that the interlayer insulating layer **26** is eliminated. The pixel layout and wiring structure in the liquid crystal display device are also similar to what is shown in FIG. **2(a)**.

[0106] Also with this construction, as in Embodiments 1 to 3, the effective reflection surfaces of the reflective layer **63** are expanded in area, so that more light can be reflected toward the display surface **40**.

[0107] Although the recesses **57** of the Cs metal layer **56** are formed in a circular shape in the embodiment above, the recesses **57** may be formed in any of various shapes, including elliptic shapes, polygonal shapes such as triangles and quadrangles, recesses with sawtoothed edges, or combinations thereof.

[0108] The liquid crystal display device of the present invention encompasses display apparatuses, television sets, mobile phones, etc., in which a liquid crystal panel

is utilized. Moreover, although the present embodiments illustrate transfective-type liquid crystal display devices as examples, a reflection-type liquid crystal display device having a similar configuration to the aforementioned reflection section would also be encompassed as one configuration of the present invention.

[0109] Moreover, since the liquid crystal display device according to the present invention is formed by the above-described manufacturing methods, it can be manufactured with the same materials and steps as those for a transmission-type liquid crystal display device. Therefore, at low cost, a liquid crystal display device having a high reflection efficiency can be provided.

INDUSTRIAL APPLICABILITY

[0110] According to the present invention, transfective-type and reflection-type liquid crystal display devices having a high image quality can be provided at low cost. Liquid crystal display devices according to the present invention can be suitably used for transfective-type and reflection-type liquid crystal display devices which perform display by utilizing reflected light, e.g., mobile phones, onboard display device such as car navigation systems, display devices of ATMs and vending machines, etc., portable display devices, laptop PCs, and the like.

Claims

1. A liquid crystal display device (10) comprising pixels (50) provided in a matrix shape on a substrate (12), source lines (52) extending along a column direction and gate lines (54) extending in a row direction, each pixel (50) including a pixel electrode (28), and a reflection region (42) for reflecting incident light toward a display surface, wherein the reflection region (42) includes a metal layer, an insulating layer (61) formed on the metal layer, and a reflective layer (63) formed on the insulating layer (61) or on a semiconductor layer (62) formed on the insulating layer (61):

a plurality of recesses (57) are formed in the metal layer in the reflection region (42);
a plurality of recesses (48) are formed in the reflective layer (63) in the reflection region (42), wherein the recesses (48) in the reflective layer (63) reflect the recesses (57) in the metal layer in position, number and shape;

characterized in that

the recesses (48) of the reflective layer (63) have a slope tilt angle with respect to the surface of the substrate of 20 degrees or less; and
an interval (a) between edge portions of two adjacent recesses (57) in the metal layer is 4 μm or less for 50% or more of the recesses (57) in

the metal layer.

2. The liquid crystal display device of claim 1, wherein the interval (a) between edge portions of at least two recesses (57) in the metal layer is 1 μm or more.
3. The liquid crystal display device of claim 1 or 2, wherein a maximum width of at least one of the plurality of recesses (57) in the metal layer is 15 μm or less.
4. The liquid crystal display device of claim 3, wherein the maximum width of at least one recess (57) in the metal layer is 2 μm or more.
5. The liquid crystal display device of any one of claims 1 to 4, wherein
In the reflection region (42) the metal layer forms a storage capacitor line (56) extending in the row direction, wherein, paired with the storage capacitor line (56) it is assigned to, each pixel electrode (28) forms a storage capacitor.
6. A method of manufacturing a liquid crystal display device comprising pixels (50) provided in a matrix shape on a substrate (12), source lines (52) extending along a column direction and gate lines (54) extending in a row direction, each pixel (50) including a pixel electrode (28) and a reflection region for reflecting incident light toward a display surface, comprising:
a step of forming a metal layer on a substrate (12);
a step of forming an insulating layer (61) on the metal layer;
a step of forming a reflective layer (63) on the insulating layer (61) or on a semiconductor layer (62) formed on the insulating layer; wherein a plurality of recesses (57) are formed in the metal layer;
in the step of forming a reflective layer (63), a plurality of recesses (48) are formed in the reflective layer (63) in the reflection region (42), wherein the recesses (48) in the reflective layer (63) reflect in position, number and shape the recesses (48) in the metal layer,
characterized in that
the recesses (48) in the reflective layer (63) are formed with a slope tilt angle with respect to the surface of the substrate of 20 degrees or less; and
an interval (a) between edge portions of at least two of the plurality of recesses (48) in the metal layer is 4 μm or less for 50% or more of the recesses (57) in the metal layer.
7. The manufacturing method of claim 6, wherein

the interval (a) between edge portions of at least two recesses (57) in the metal layer is 1 μm or more.

8. The manufacturing method of claim 6 or 7, wherein a maximum width of at least one of the plurality of recesses (57) in the metal layer is 15 μm or less. 5
9. The manufacturing method of claim 8, wherein the maximum width of at least one recess (57) in the metal layer is 2 μm or more. 10
10. The manufacturing method of any one of claims 6 to 9, wherein in the reflection region (42) the metal layer forms a storage capacitor line (56) extending in the row direction, wherein, paired with the storage capacitor line (56) it is assigned to, each pixel electrode (28) forms a storage capacitor. 15
11. The manufacturing method of claim 10, wherein in the step of forming the storage capacitor line (56), photolithography technique is used to form the plurality of recesses (57); and a thickness of a resist film used for forming the plurality of recesses (57) is smaller than that of a resist film used for forming the storage capacitor line (56). 20 25

Patentansprüche

1. Flüssigkristallanzeigeeinrichtung (10), mit:

Pixeln (50), die in einer Matrixform auf einem Substrat (12) ausgebildet sind, Sourceleitungen (52), die sich entlang einer Spaltenrichtung erstrecken, und Gateleitungen (54), die sich entlang einer Zeilenrichtung erstrecken, wobei jedes Pixel (50) eine Pixelelektrode (28) und ein Reflexionsgebiet (42) zum Reflektieren einfallenden Lichts auf eine Anzeigefläche hin aufweist, wobei das Reflexionsgebiet (42) eine Metallschicht, eine Isolationsschicht (61), die auf der Metallschicht ausgebildet ist, und eine Reflexionsschicht (63), die auf der Isolationsschicht (61) ausgebildet ist oder einer Halbleiterschicht (62), die auf der Isolationsschicht (61) ausgebildet ist, aufweist, einer Mehrzahl von Ausnehmungen (57), die in der Metallschicht im Reflexionsgebiet (42) ausgebildet sind, einer Mehrzahl von Ausnehmungen (48), die in der Reflexionsschicht (63) im Reflexionsgebiet (42) ausgebildet sind, wobei die Ausnehmungen (48) in der Reflexionsschicht (63) die Ausnehmungen (57) in der Metallschicht in Position, Anzahl und Gestalt wiedergeben,

dadurch gekennzeichnet,

dass die Ausnehmungen (48) der Reflexionsschicht (63) einen in Bezug auf die Oberfläche des Substrats geneigten Böschungswinkel von 20 Grad oder weniger aufweisen und

dass ein Abstand (a) zwischen Kantenbereichen zweier benachbarter Ausnehmungen (57) in der Metallschicht 4 μm oder weniger für 50 % oder mehr der Ausnehmungen (57) in der Metallschicht beträgt.

2. Flüssigkristallanzeigeeinrichtung nach Anspruch 1, wobei der Abstand (a) zwischen Kantenbereichen von mindestens zwei Ausnehmungen (57) in der Metallschicht 1 μm oder mehr beträgt. 15
3. Flüssigkristallanzeigeeinrichtung nach Anspruch 1 oder 2, wobei eine maximale Breite mindestens einer der Mehrzahl von Ausnehmungen (57) in der Metallschicht 50 μm oder weniger beträgt. 20
4. Flüssigkristallanzeigeeinrichtung nach Anspruch 3, wobei die maximale Breite mindestens einer Ausnehmung (57) in der Metallschicht 2 μm oder mehr beträgt. 25
5. Flüssigkristallanzeigeeinrichtung nach einem der Ansprüche 1 bis 4, wobei in dem Reflexionsgebiet (42) die Metallschicht eine Speicherkondensatorleitung (56) bildet, die sich in der Zeilenrichtung erstreckt, wobei jede Pixelelektrode (28) gepaart mit der Speicherkondensatorleitung (56), der sie zugeordnet ist, einen Speicherkondensator bildet. 30 35
6. Verfahren zum Herstellen einer Flüssigkristallanzeigeeinrichtung mit Pixeln (50), die in einer Matrixform auf einem Substrat (12) ausgebildet sind, Sourceleitungen (52), die sich entlang einer Spaltenrichtung erstrecken, und Gateleitungen (54), die sich entlang einer Zeilenrichtung erstrecken, wobei jedes Pixel (50) eine Pixelelektrode (28) und ein Reflexionsgebiet (42) zum Reflektieren einfallenden Lichts auf eine Anzeigefläche hin aufweist, mit:

einem Schritt des Ausbildens einer Metallschicht auf einem Substrat (12),
 einem Schritt des Ausbildens einer Isolationsschicht (61) auf der Metallschicht,
 einem Schritt des Ausbildens einer Reflexionsschicht (63) auf der Isolationsschicht (61) oder auf einer Halbleiterschicht (62), die auf der Isolationsschicht ausgebildet ist,

wobei:

- eine Mehrzahl von Ausnehmungen (57) in der Metallschicht ausgebildet wird,
 beim Schritt des Ausbildens einer Reflexionsschicht (63) eine Mehrzahl von Ausnehmungen (48) in der Reflexionsschicht (63) im Reflexionsgebiet (42) ausgebildet wird, wobei die Ausnehmungen (48) in der Reflexionsschicht (63) die Ausnehmungen (48) in der Metallschicht in Position, Anzahl und Gestalt wiedergeben,
dadurch gekennzeichnet,
dass die Ausnehmungen (48) in der Reflexionsschicht (63) in Bezug auf die Oberfläche des Substrats mit einem geneigten Böschungswinkel von 20 Grad oder weniger ausgebildet werden und
dass ein Abstand (a) zwischen Kantenbereichen von mindestens zwei der Mehrzahl von Ausnehmungen (48) in der Metallschicht 4 μm oder weniger beträgt für 50 % oder mehr der Ausnehmungen (57) in der Metallschicht.
7. Herstellungsverfahren nach Anspruch 6, wobei der Abstand (a) zwischen Kantenbereichen von mindestens zwei Ausnehmungen (57) in der Metallschicht 1 μm oder mehr beträgt.
 8. Herstellungsverfahren nach Anspruch 6 oder 7, wobei eine maximale Breite mindestens einer der Mehrzahl von Ausnehmungen (57) in der Metallschicht 15 μm oder weniger beträgt.
 9. Herstellungsverfahren nach Anspruch 8, wobei die maximale Breite mindestens einer Ausnehmung (57) in der Metallschicht 2 μm oder mehr beträgt.
 10. Herstellungsverfahren nach einem der Ansprüche 6 bis 9, wobei in dem Reflexionsgebiet (42) die Metallschicht eine Speicherkondensatorleitung (56) bildet, die sich in der Zeilenrichtung erstreckt, wobei jede Pixelelektrode (28) gepaart mit der Speicherkondensatorleitung (56), der sie zugeordnet ist, einen Speicherkondensator bildet.
 11. Herstellungsverfahren nach Anspruch 10, wobei:

beim Schritt des Ausbildens der Speicherkondensatorleitung (56) eine Fotolithographietechnik verwendet wird, um die Mehrzahl von Ausnehmungen (57) auszubilden, und
 die Dicke einer Resistschicht, die zum Ausbilden der Mehrzahl von Ausnehmungen (57) verwendet wird, geringer ist als diejenige einer Resistschicht, die zum Ausbilden der Speicherkondensatorleitung (56) verwendet wird.

Revendications

1. Dispositif d'affichage à cristaux liquides (10) comprenant
 des pixels (50) qui sont disposés suivant une forme de matrice sur un substrat (12), des lignes de source (52) s'étendant le long d'une direction de colonne, et des lignes de porte (54) s'étendant dans une direction de rangée, chaque pixel (50) contenant une électrode de pixel (28) et une zone de réflexion (42) pour réfléchir la lumière incidente vers une surface d'affichage,
 étant précisé que la zone de réflexion (42) contient une couche métallique, une couche isolante (61) formée sur la couche métallique, et une couche réfléchissante (63) formée sur la couche isolante (61) ou sur une couche semiconductrice (62) formée sur la couche isolante (61) ;
 que plusieurs creux (57) sont formés dans la couche métallique prévue dans la zone de réflexion (42) ;
 que plusieurs creux (48) sont formés dans la couche réfléchissante (63) prévue dans la zone de réflexion (42), étant précisé que les creux (48) prévus dans la couche réfléchissante (63) correspondent par leur position, leur nombre et leur forme aux creux (57) prévus dans la couche métallique ;
caractérisé en ce que les creux (48) de la couche réfléchissante (63) ont un angle d'inclinaison de pente, par rapport à la surface du substrat, de 20 degrés ou moins ; et
en ce qu'un intervalle (a) entre les parties de bord de deux creux (57) voisins prévus dans la couche métallique est de 4 μm ou moins pour 50 % ou plus des creux (57) prévus dans la couche métallique.
2. Dispositif d'affichage à cristaux liquides de la revendication 1, étant précisé
 que l'intervalle (a) entre les parties de bord d'au moins deux creux (57) prévus dans la couche métallique est de 1 μm ou plus.
3. Dispositif d'affichage à cristaux liquides de la revendication 1 ou 2, étant précisé
 qu'une largeur maximale de l'un au moins des creux (57) prévus dans la couche métallique est de 15 μm ou moins.
4. Dispositif d'affichage à cristaux liquides de la revendication 3, étant précisé
 que la largeur maximale d'au moins un creux (57) prévu dans la couche métallique est de 2 μm ou plus.
5. Dispositif d'affichage à cristaux liquides de l'une quelconque des revendications 1 à 4, étant précisé
 que dans la zone de réflexion (42), la couche métallique forme une ligne de condensateur de mémorisation (56) qui s'étend dans le sens de rangée, étant précisé que couplée à la ligne de condensateur de

mémorisation (56) à laquelle elle est affectée, chaque électrode de pixel (28) forme un condensateur de mémorisation.

6. Procédé pour fabriquer un dispositif d'affichage à cristaux liquides comprenant des pixels (50) qui sont disposés suivant une forme de matrice sur un substrat (12), des lignes de source (52) s'étendant le long d'une direction de colonne, et des lignes de porte (54) s'étendant dans une direction de rangée, chaque pixel (50) contenant une électrode de pixel (28) et une zone de réflexion (42) pour réfléchir la lumière incidente vers une surface d'affichage, comprenant :
 - une étape de formation d'une couche métallique sur un substrat (12) ;
 - une étape de formation d'une couche isolante (61) sur la couche métallique ;
 - une étape de formation d'une couche réfléchissante (63) sur la couche isolante (61) ou sur une couche semiconductrice (62) formée sur la couche isolante ; étant précisé que plusieurs creux (57) sont formés dans la couche métallique ;
 - que lors de l'étape de formation d'une couche réfléchissante (63), plusieurs creux (48) sont formés dans la couche réfléchissante (63) prévue dans la zone de réflexion (42), étant précisé que les creux (48) prévus dans la couche réfléchissante (63) correspondent par leur position, leur nombre et leur forme aux creux (48) prévus dans la couche métallique,
 - caractérisé en ce que** les creux (48) prévus dans la couche réfléchissante (63) sont formés avec un angle d'inclinaison de pente, par rapport à la surface du substrat, de 20 degrés ou moins ;
 - et
 - en ce qu'un** intervalle (a) entre les parties de bord d'au moins deux des creux (48) prévus dans la couche métallique est de 4 μm ou moins pour 50 % ou plus des creux (57) prévus dans la couche métallique.
7. Procédé de fabrication de la revendication 6, étant précisé que l'intervalle (a) entre les parties de bord d'au moins deux creux (57) prévus dans la couche métallique est de 1 μm ou plus.
8. Procédé de fabrication de la revendication 6 ou 7, étant précisé qu'une largeur maximale de l'un au moins des creux (57) prévus dans la couche métallique est de 15 μm ou moins.
9. Procédé de fabrication de la revendication 8, étant précisé que la largeur maximale d'au moins un creux (57) prévu dans la couche métallique est de 2 μm ou plus.

10. Procédé de fabrication de l'une quelconque des revendications 6 à 9, étant précisé que dans la zone de réflexion (42), la couche métallique forme une ligne de condensateur de mémorisation (56) qui s'étend dans le sens de rangée, étant précisé que couplée à la ligne de condensateur de mémorisation (56) à laquelle elle est affectée, chaque électrode de pixel (28) forme un condensateur de mémorisation.
11. Procédé de fabrication de la revendication 10, étant précisé que lors de l'étape de formation de la ligne de condensateur de mémorisation (56), une technique de photolithographie est utilisée pour former les creux (57) ; et qu'une épaisseur d'un film de résist utilisé pour former les creux (57) est inférieure à celle d'un film de résist utilisé pour former la ligne de condensateur de mémorisation (56).

FIG. 1

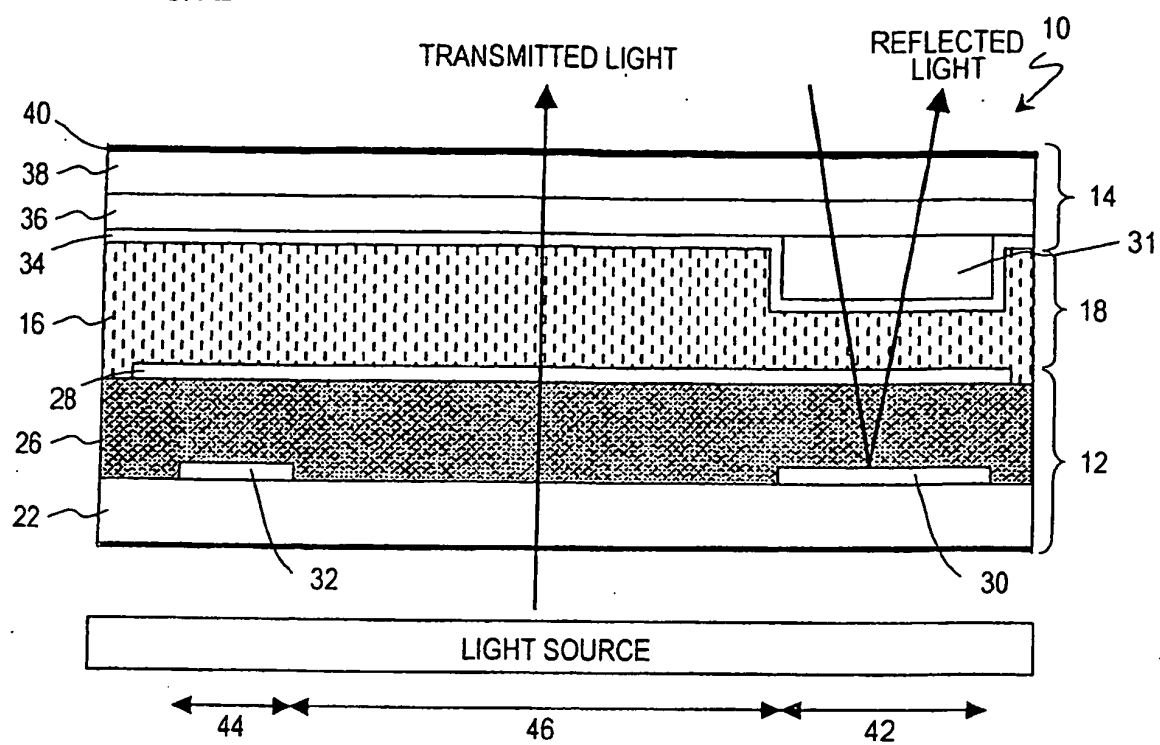


FIG. 2

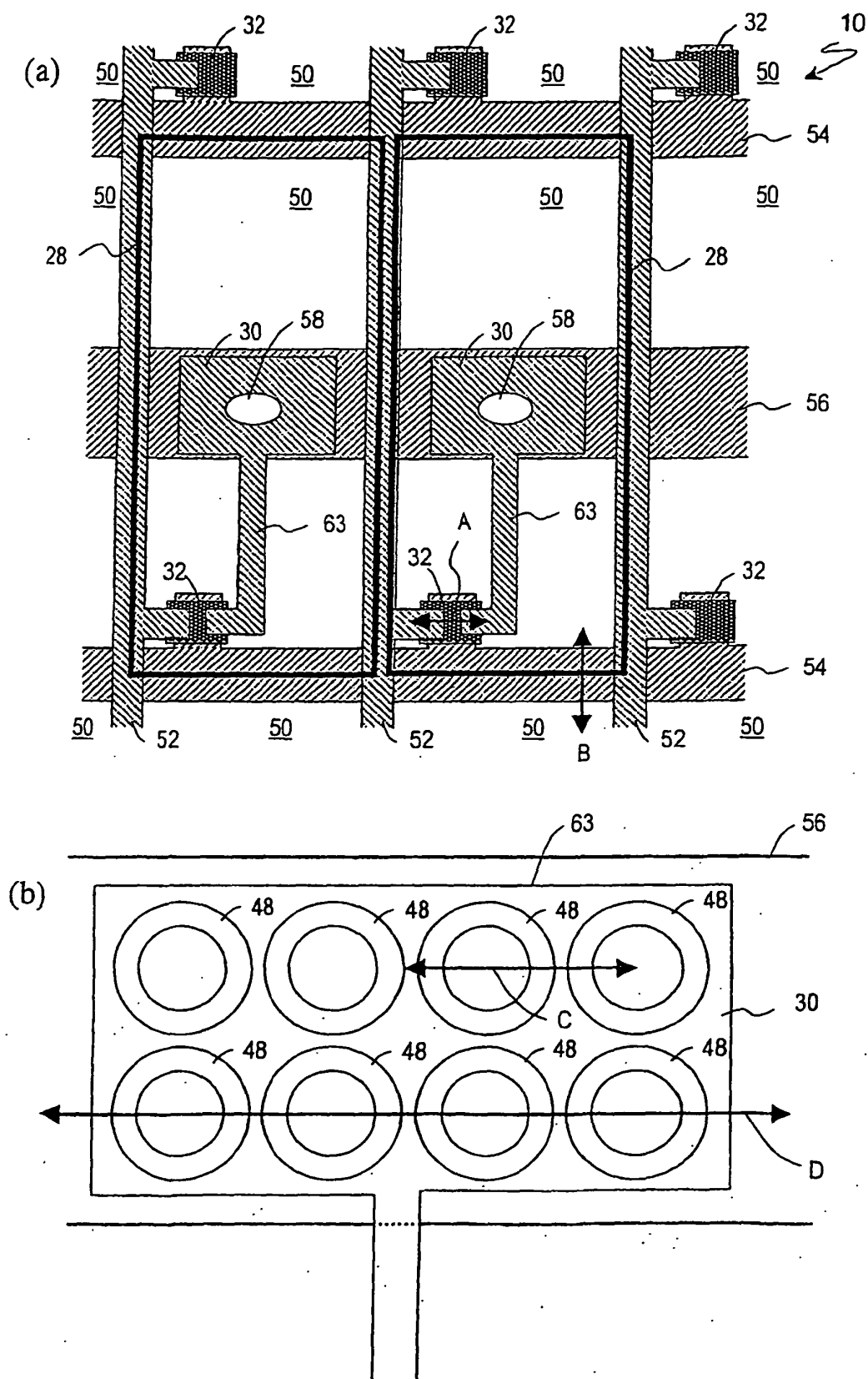


FIG. 3

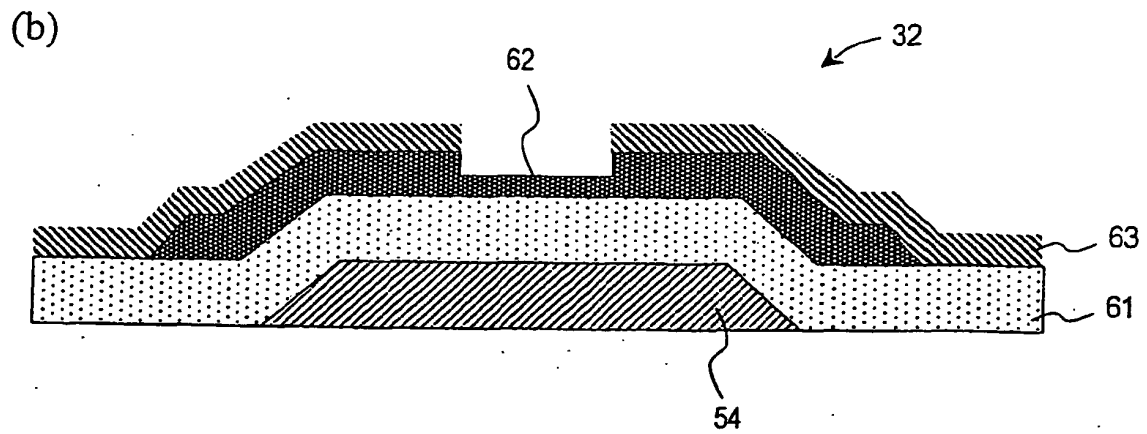
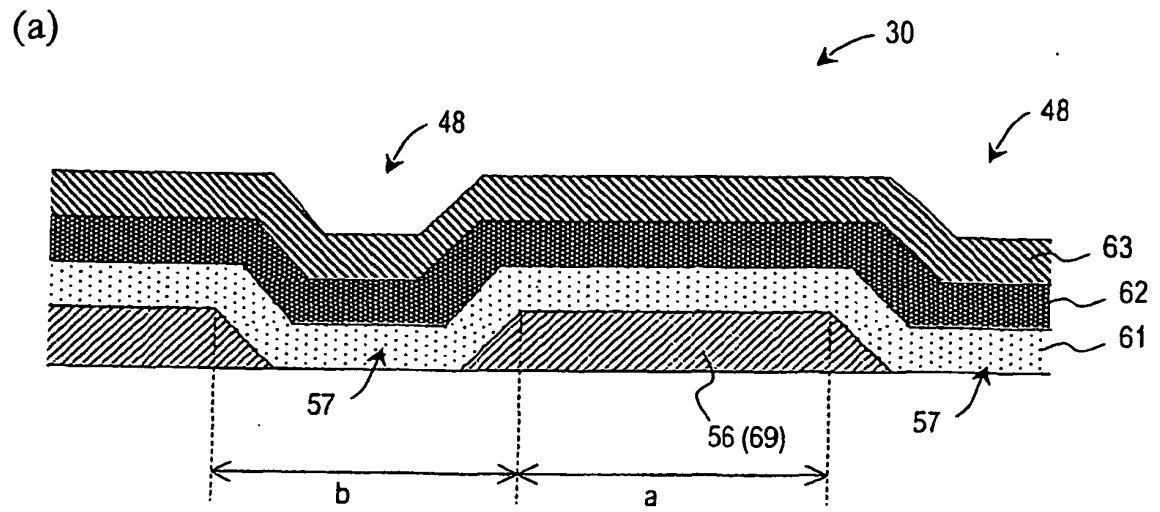


FIG. 4

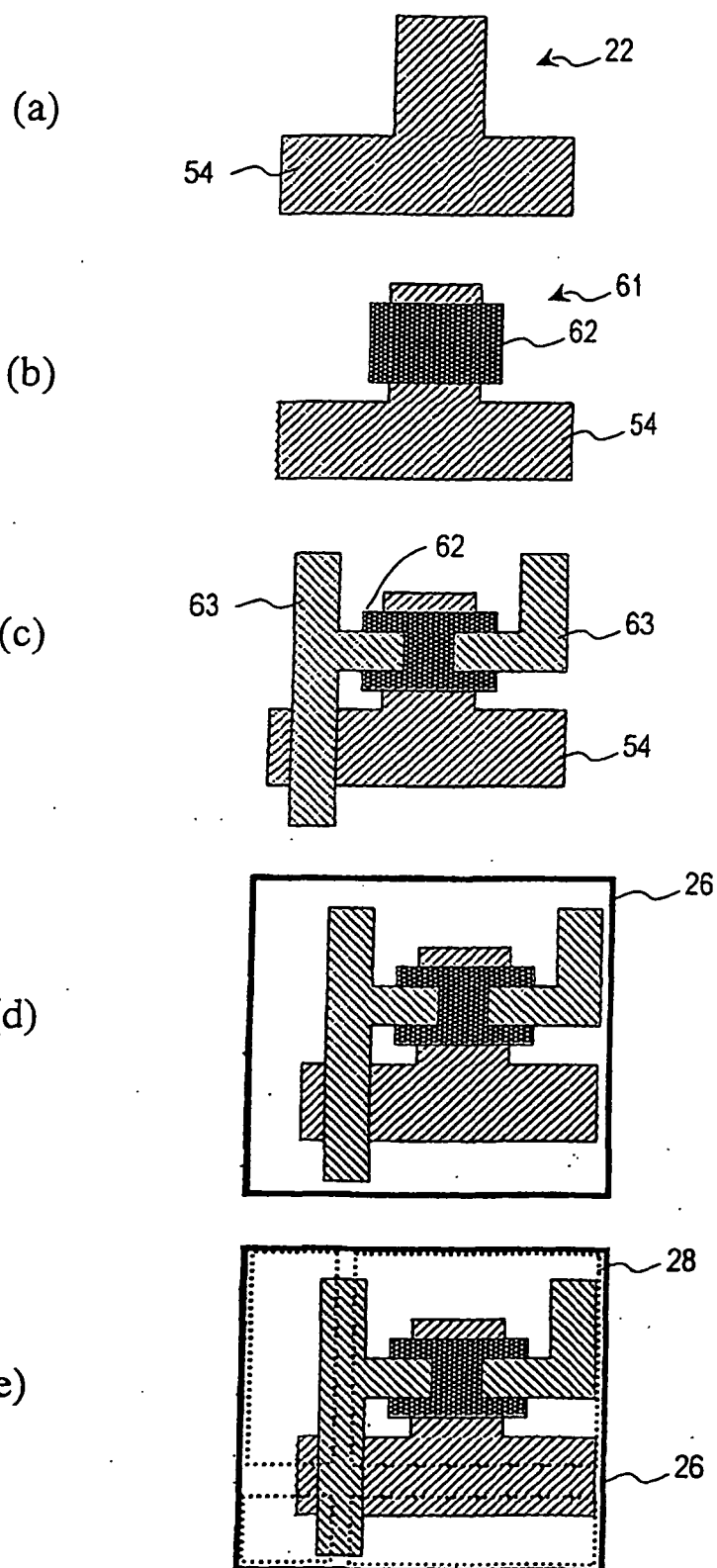
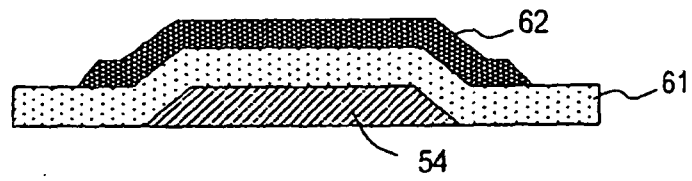


FIG. 5

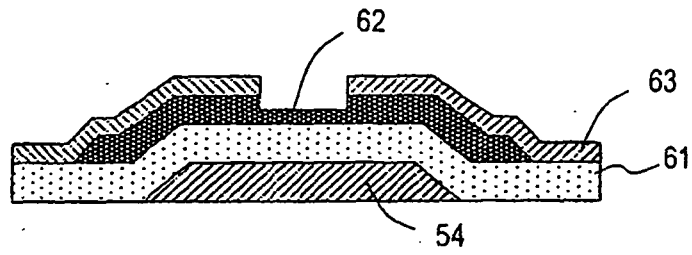
(a)



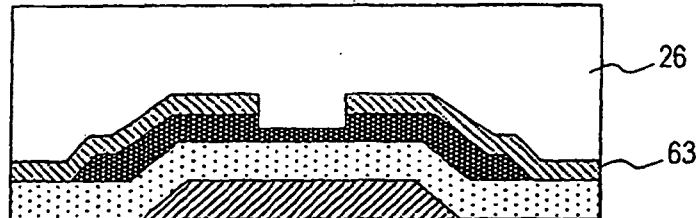
(b)



(c)



(d)



(e)

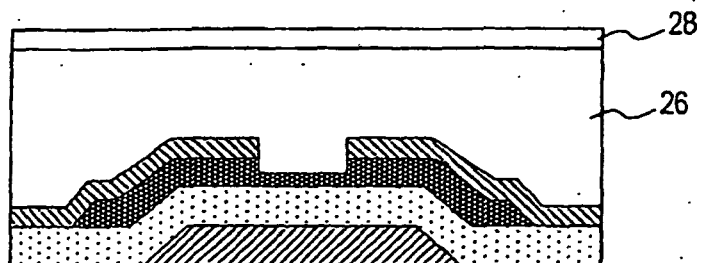


FIG. 6

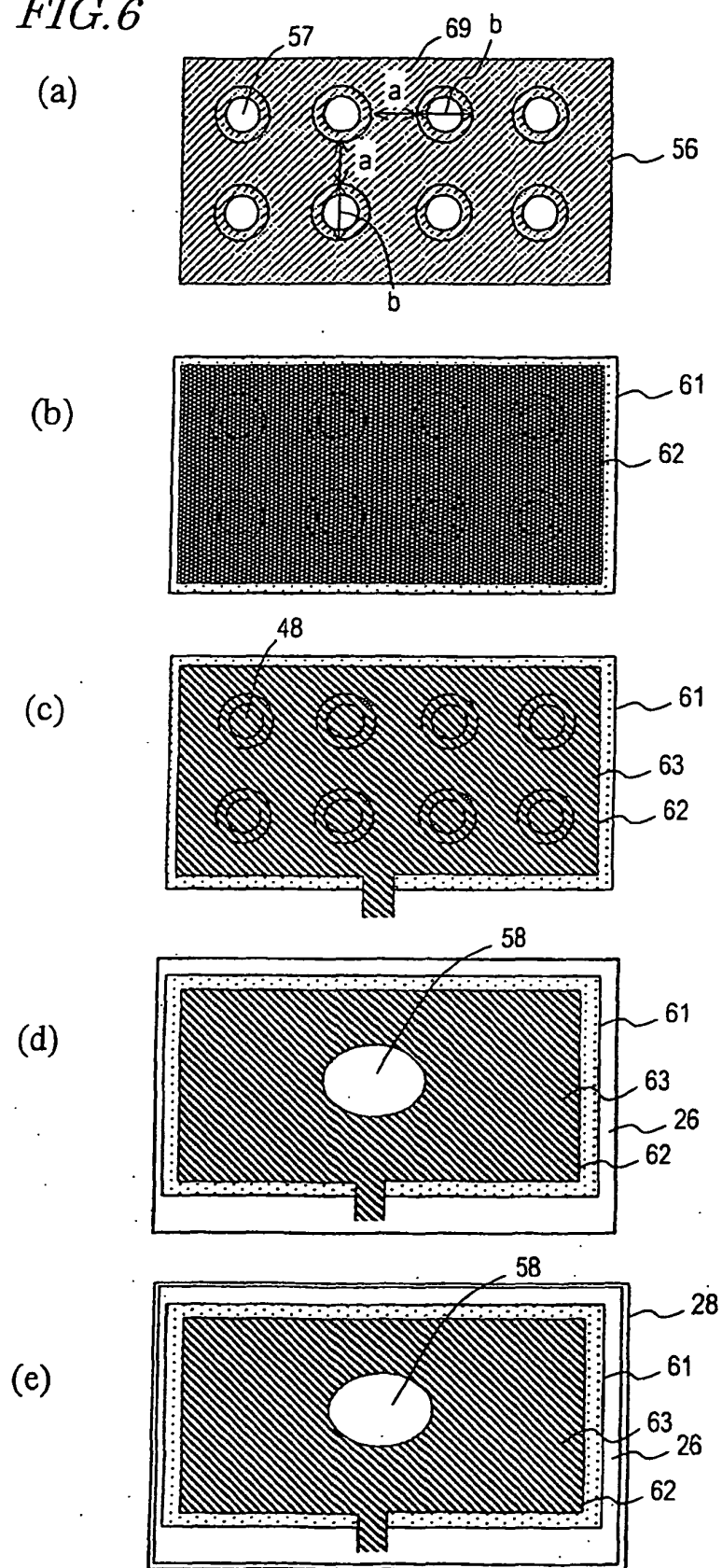


FIG. 7

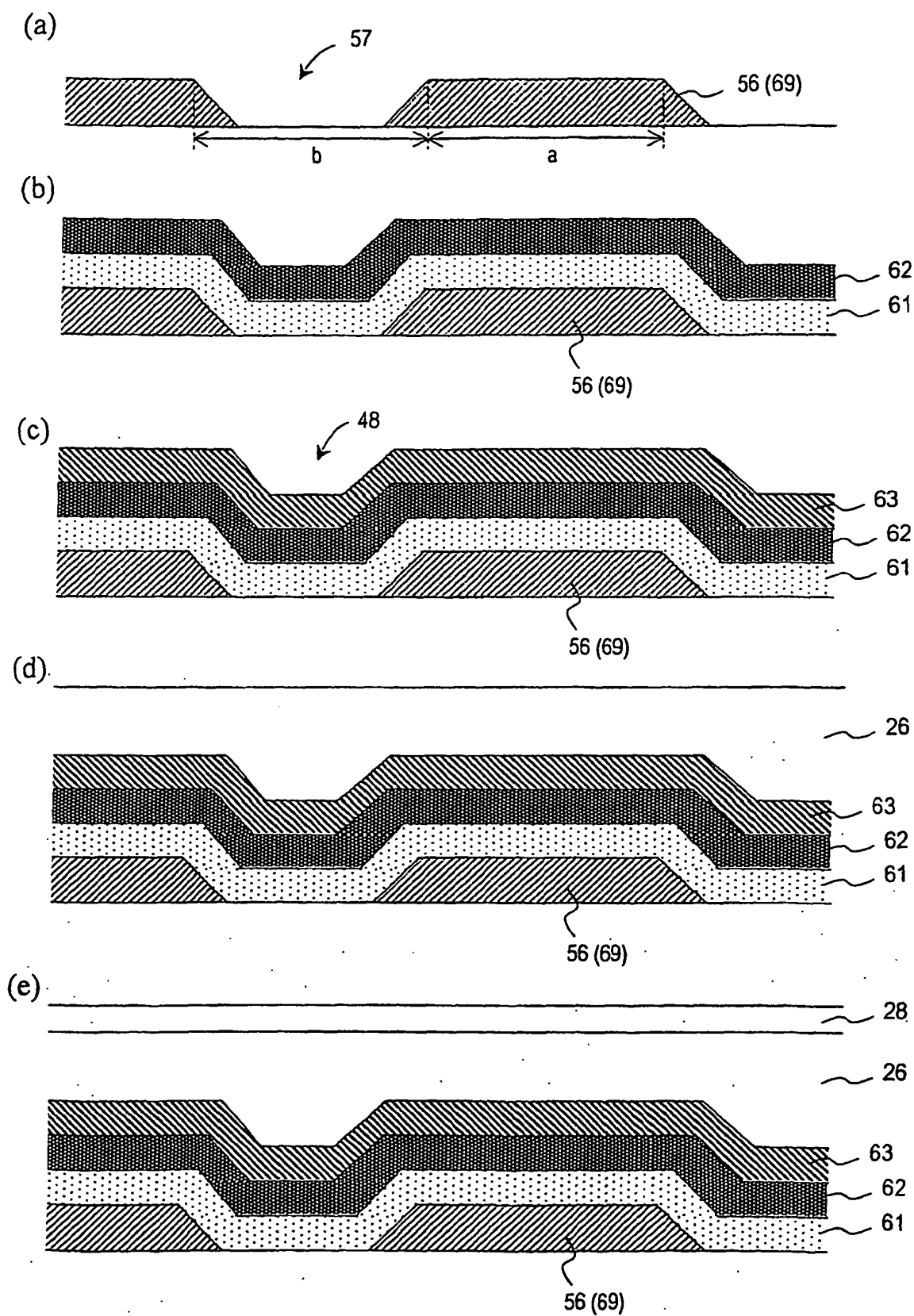
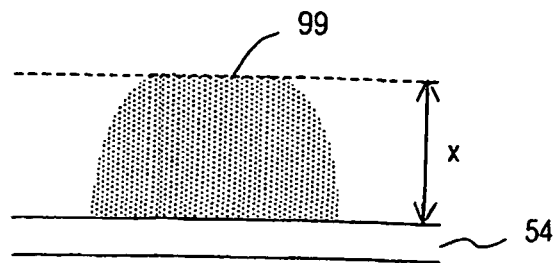


FIG. 8

(a)



(b)

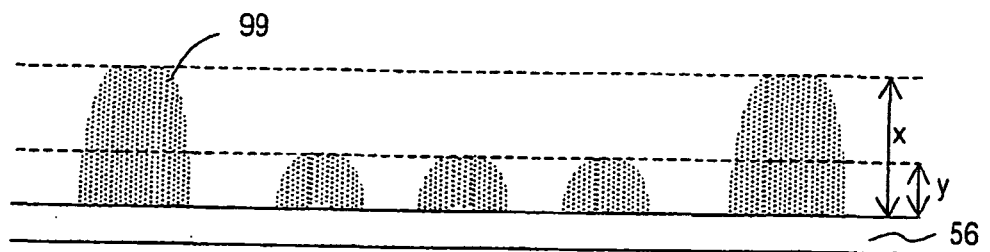


FIG. 9

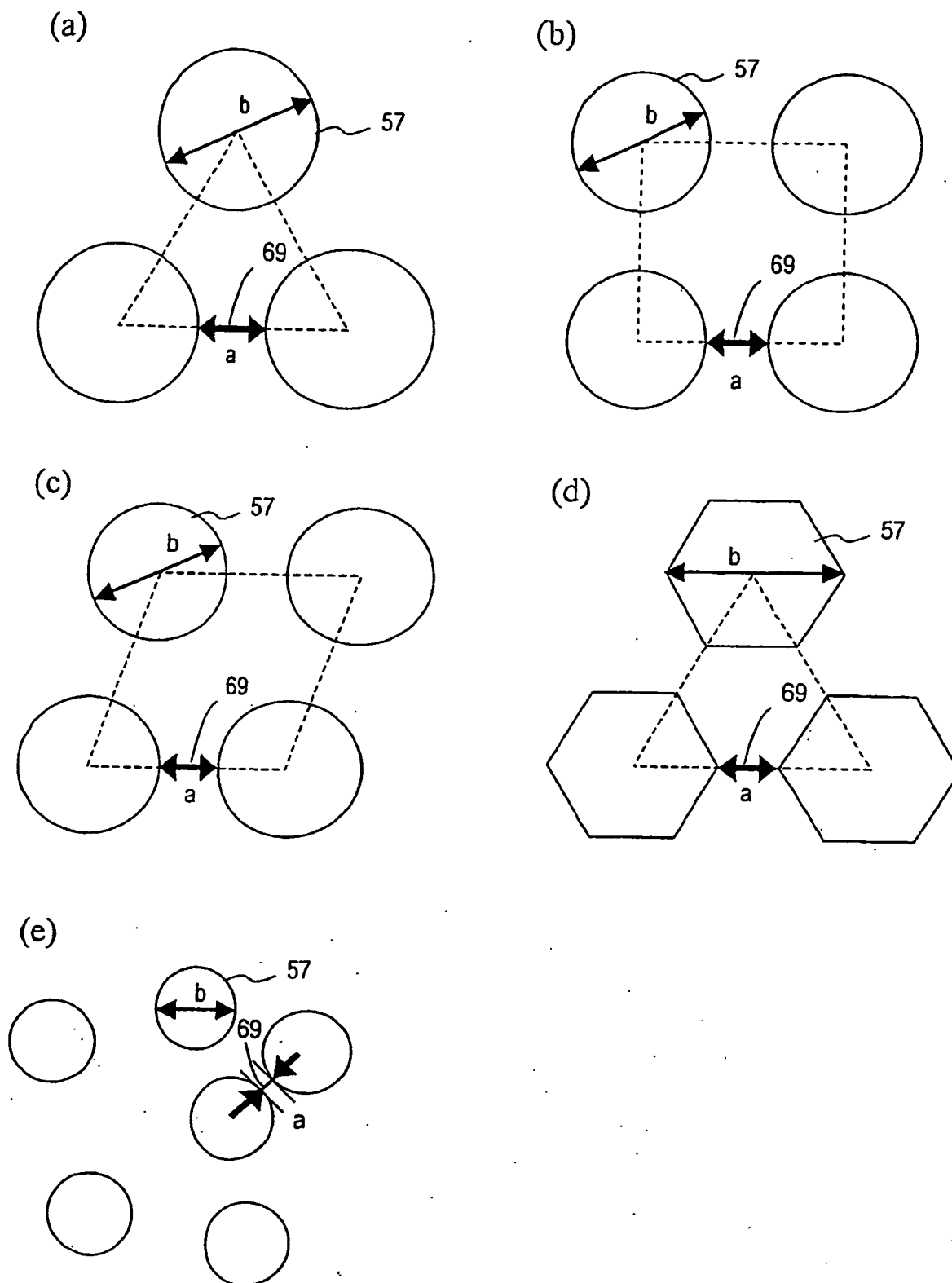


FIG. 10

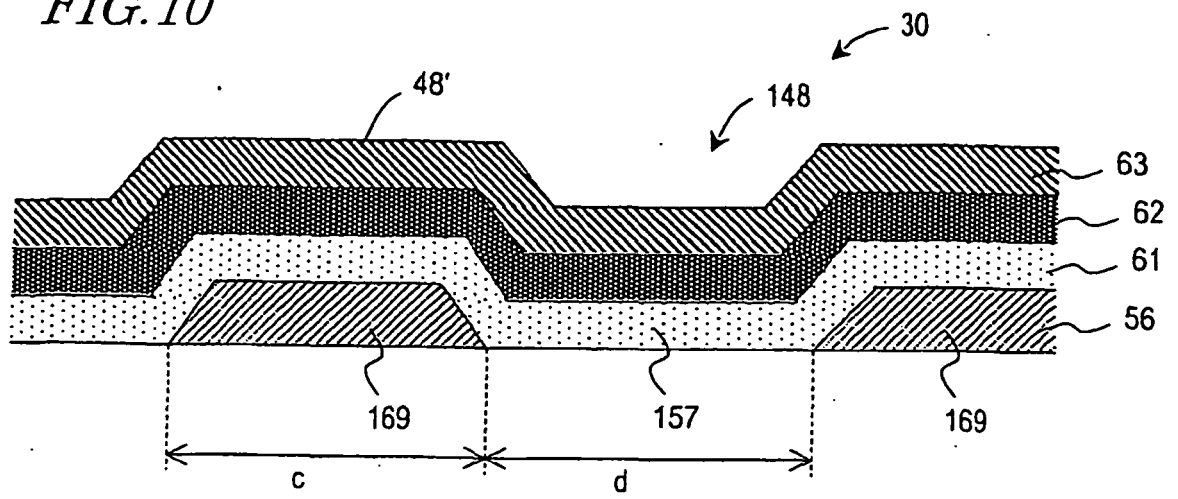
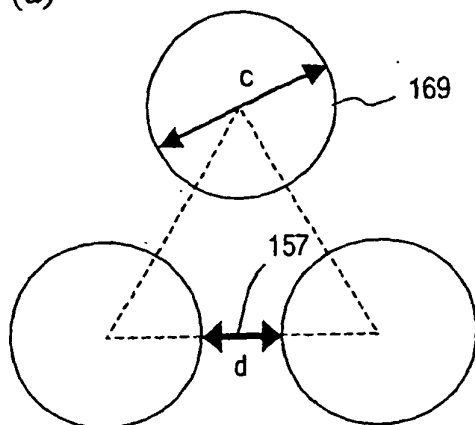
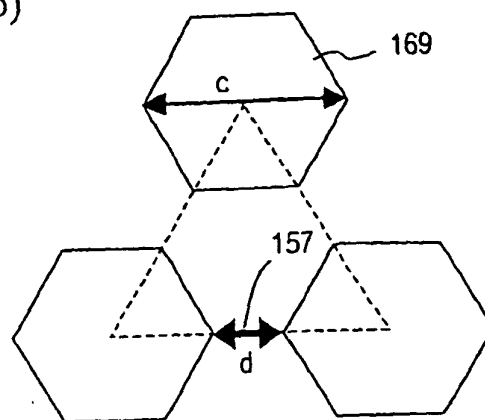


FIG. 11

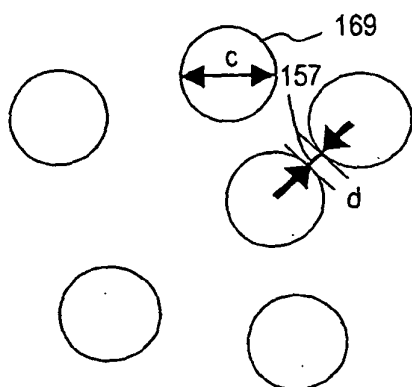
(a)



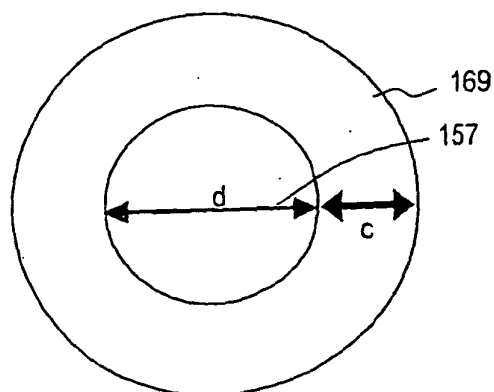
(b)



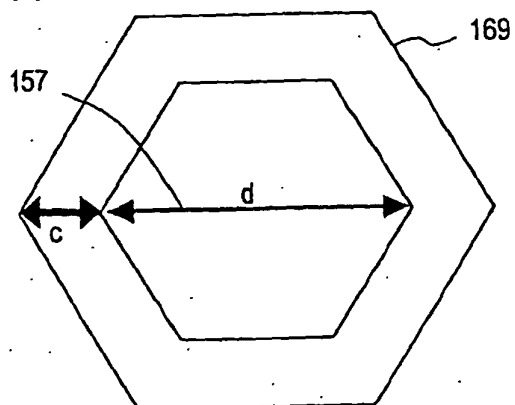
(c)



(d)



(e)



(f)

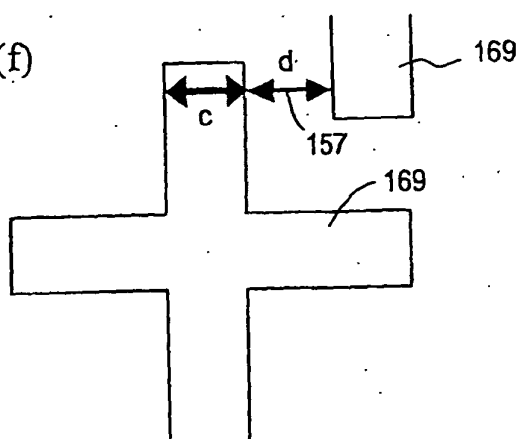


FIG. 12

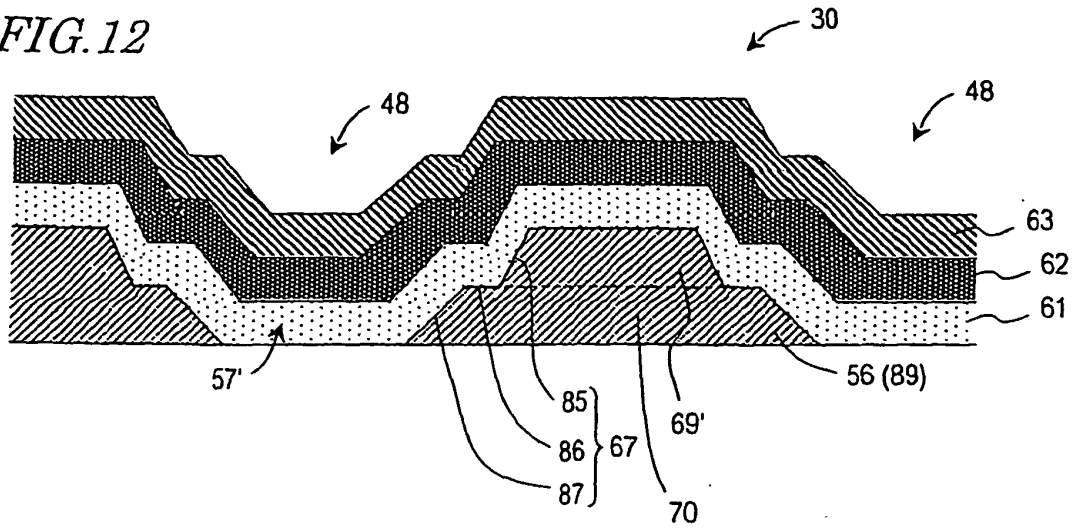
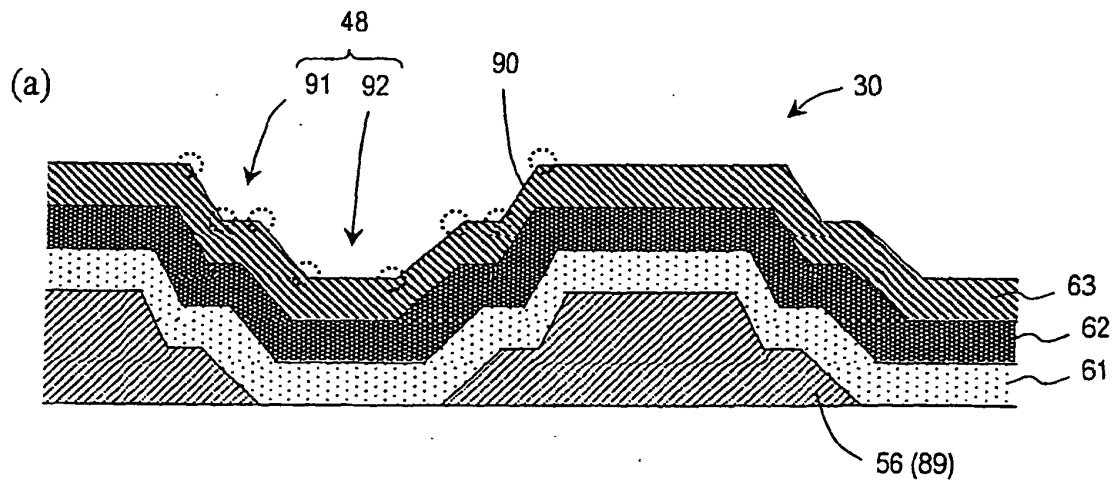
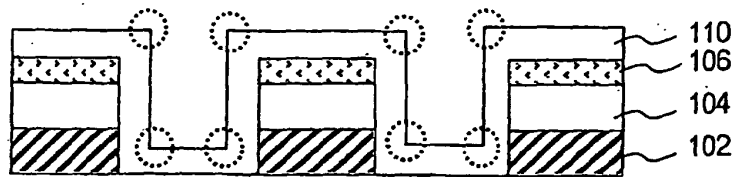


FIG. 13



(b)



(c)

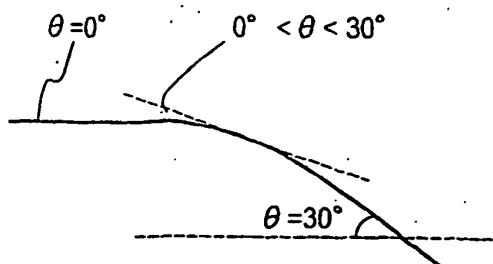


FIG. 14

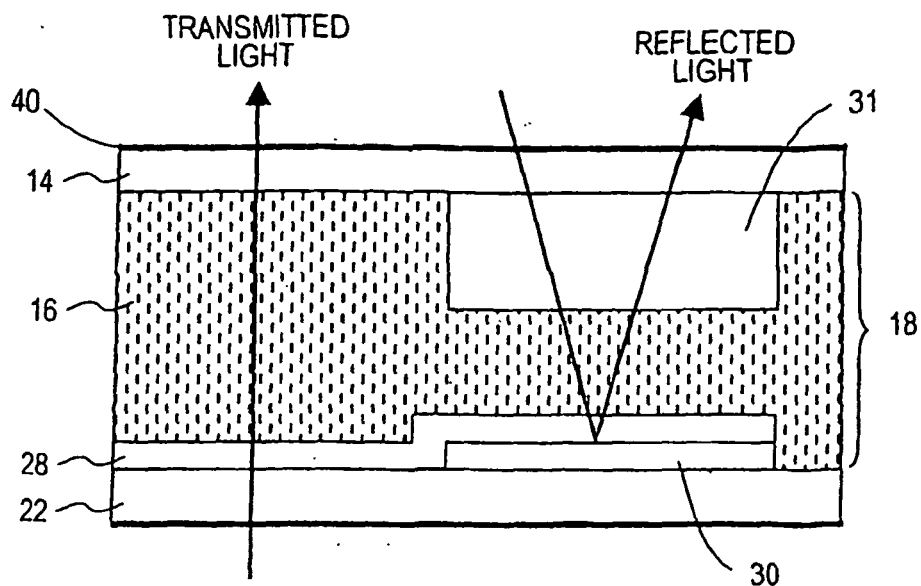


FIG. 15

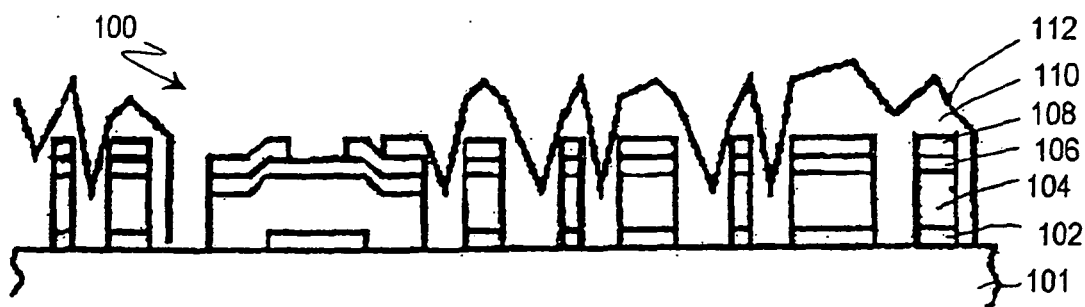
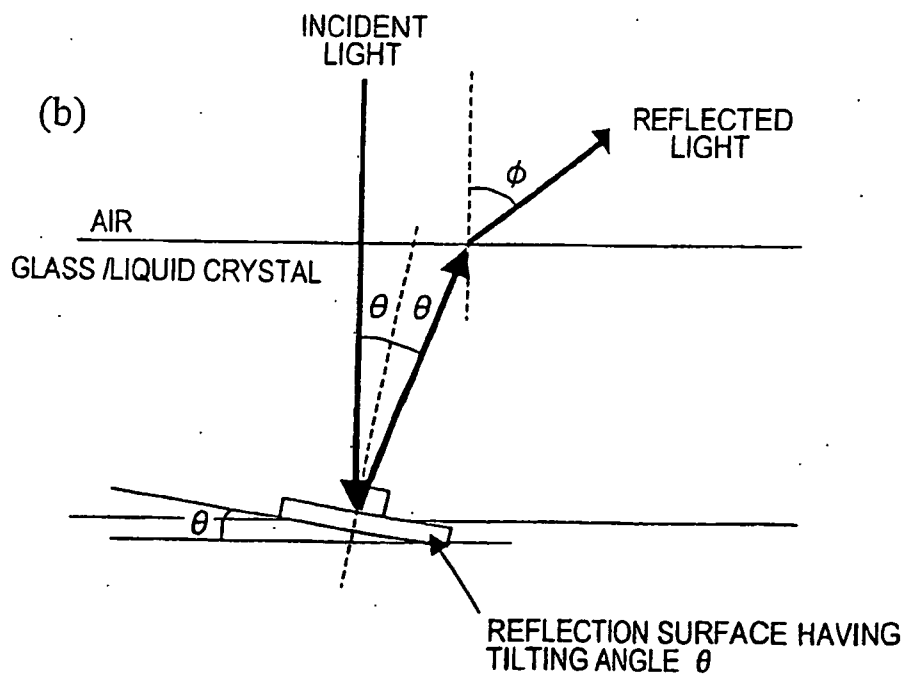
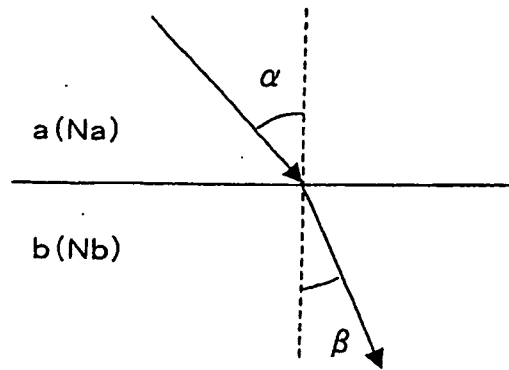


FIG.16

(a)



REFERENCES CITED IN THE DESCRIPTION

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专利名称(译)	液晶显示器和制造液晶显示器的方法		
公开(公告)号	EP2085813B1	公开(公告)日	2014-01-01
申请号	EP2007806943	申请日	2007-09-07
[标]申请(专利权)人(译)	夏普株式会社		
申请(专利权)人(译)	夏普株式会社		
当前申请(专利权)人(译)	夏普株式会社		
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发明人	HARA, YOSHIHITO KIKUCHI, TETSUO KITAGAWA, HIDEKI IMAI, HAJIME IMADE, MITSUNORI SHIMADA, JUNYA		
IPC分类号	G02F1/1335 G02F1/1343		
CPC分类号	G02F1/133553		
优先权	2006284206 2006-10-18 JP		
其他公开文献	EP2085813A4 EP2085813A1		
外部链接	Espacenet		

摘要(译)

提供一种具有高反射效率和高图像质量的半透射型和反射型液晶显示装置。本发明的液晶显示装置是包括用于朝向显示表面反射入射光的反射区域的液晶显示装置,其中反射区域包括金属层,形成在金属层上的绝缘层,形成的半导体层在绝缘层上,和在半导体层上形成的反射层;在金属层,绝缘层和半导体层中的至少一个中形成多个凹槽;根据所述多个凹槽,在反射区域的反射层中形成多个凹痕;并且,多个凹部中的至少两个的边缘部分之间的最短距离a为4 μ m或更小。

